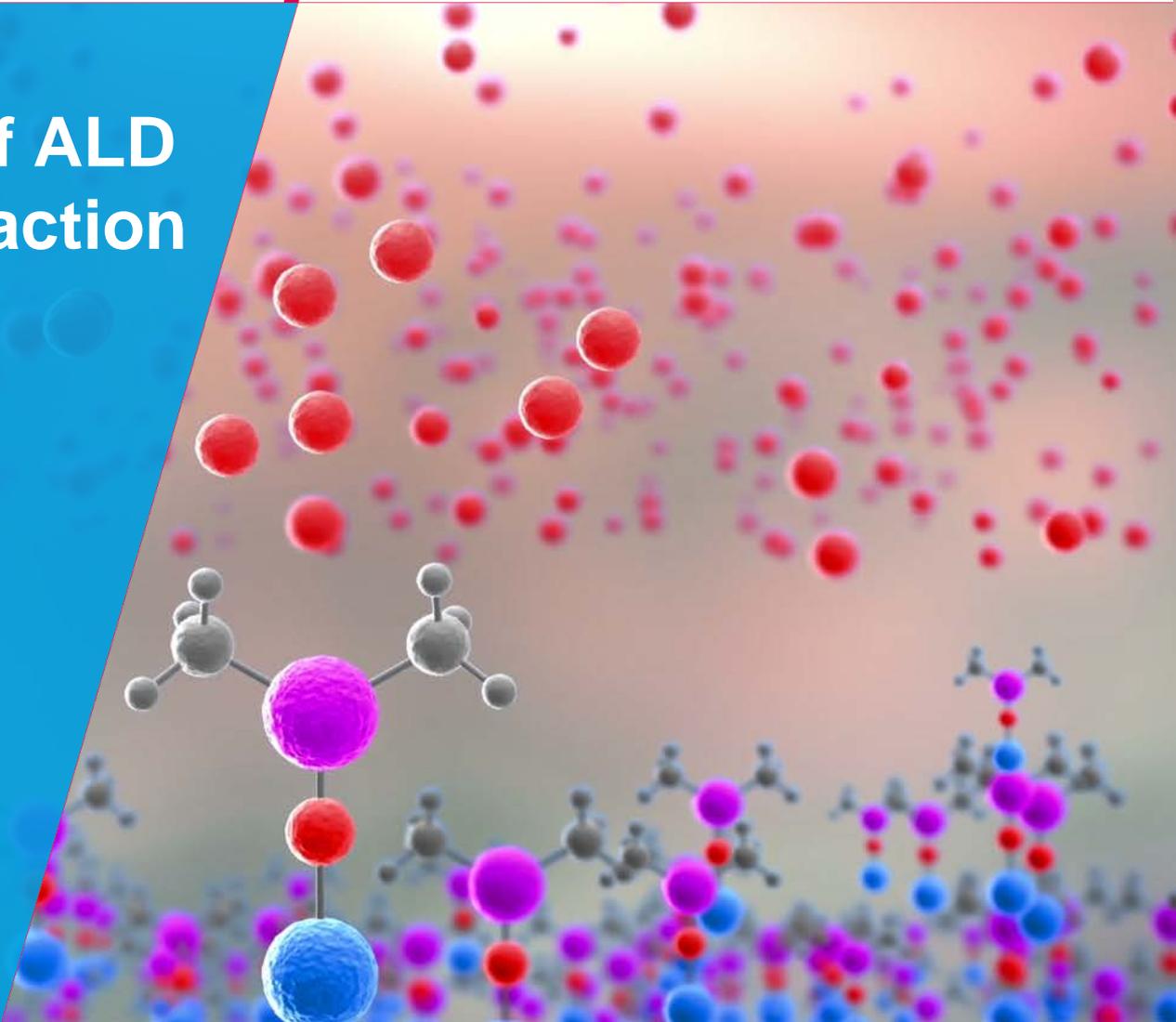


# *In situ* Studies of ALD Processes & Reaction Mechanisms

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www.tue.nl/pmp



# This tutorial presentation will give ...

- (1) an overview of **methods** for *in situ* studies of ALD processes & reaction mechanisms; and
- (2) some **insight** into these processes and mechanisms

Don't expect:

- A comprehensive overview
- Techniques explained in large detail

Do expect:

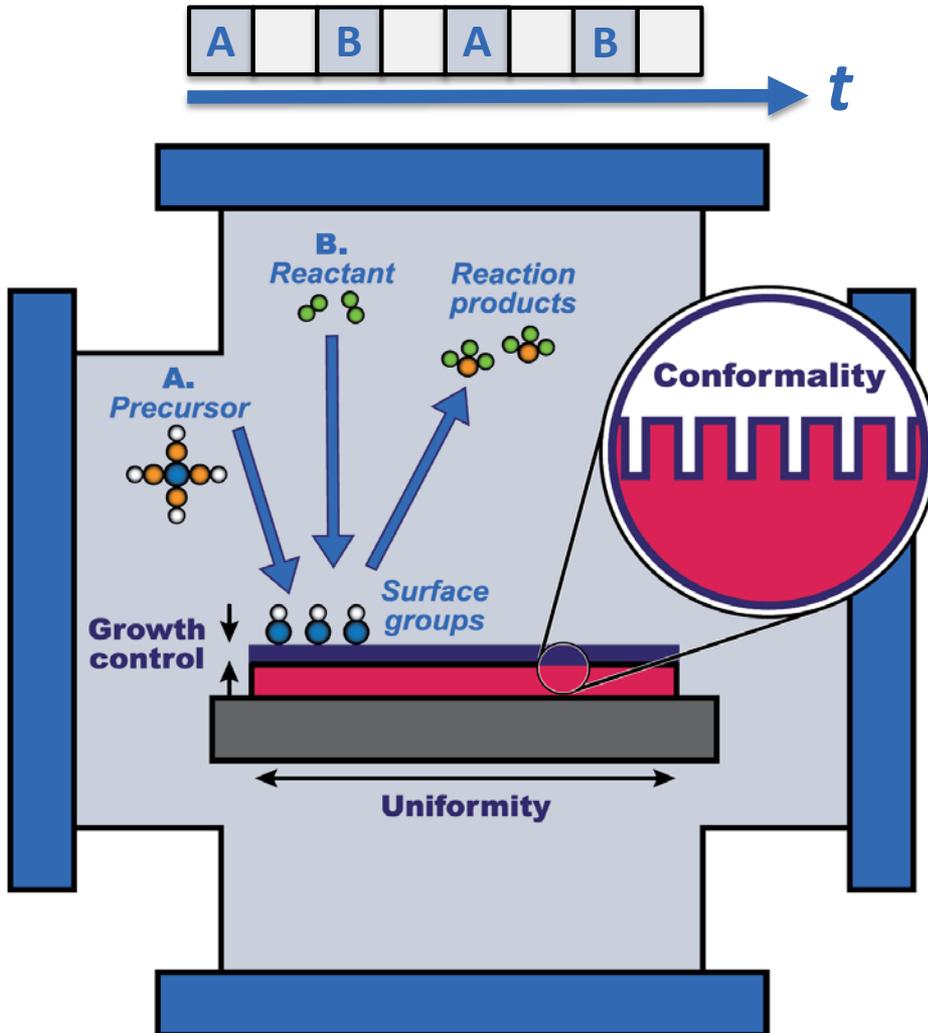
- Focus on what can be learned from the methods
- Their pros and cons articulated & practical comments
- An overview based mainly from own experience



For more information & feedback  
see blog:

[www.AtomicLimits.com](http://www.AtomicLimits.com)

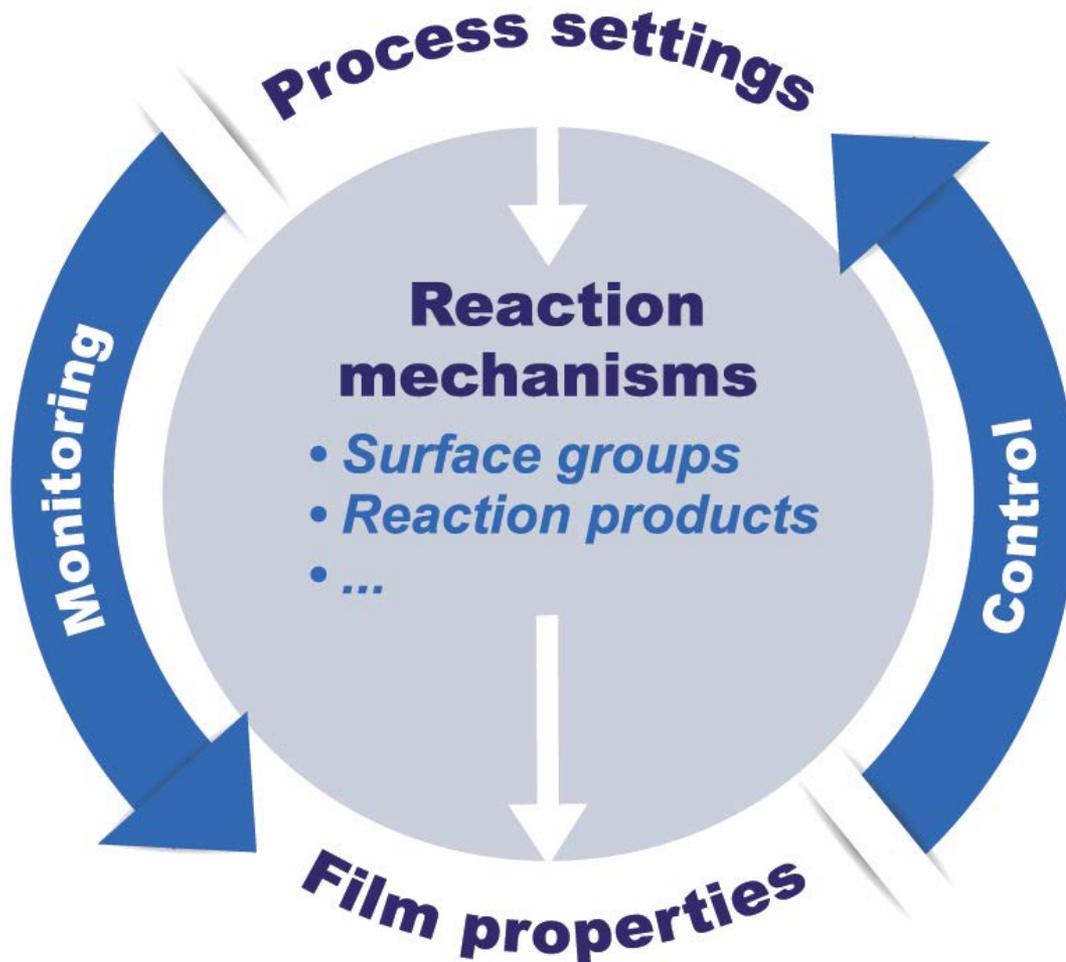
# Atomic layer deposition (ALD)



## *In situ* studies:

- Quartz crystal microbalance
- Spectroscopic ellipsometry
- Mass spectrometry
- Gas phase infrared spect.
- Surface infrared spect.
- Optical emission spect.
- X-ray photoelectron spect.
- X-ray diffraction
- Sum-frequency generation
- Adsorption calorimetry
- Scanning tunneling micros.
- ...

# In situ studies of ALD processes



## Discussed **today**:

- Quartz crystal microbalance
- Spectroscopic ellipsometry
- Mass spectrometry
- Gas phase infrared spect.
- Surface infrared spect.
- Optical emission spect.
  
- X-ray photoelectron spect.
- X-ray diffraction
- **Sum-frequency generation**
- **Adsorption calorimetry**
- Scanning tunneling micros.
- ...

# In situ studies of ALD processes

## ADEQUACY



## FEASIBILITY



## COMPLEXITY



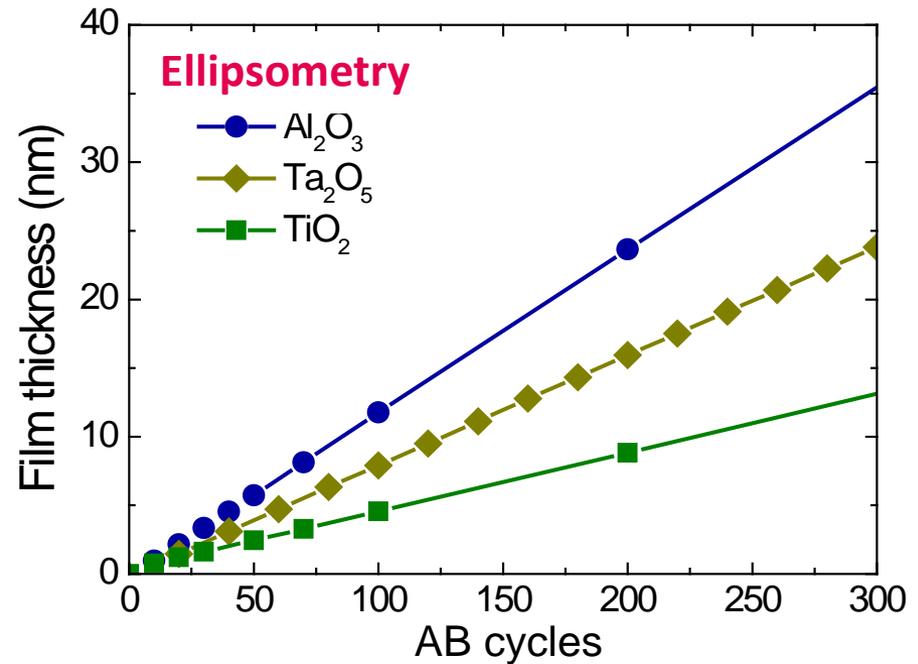
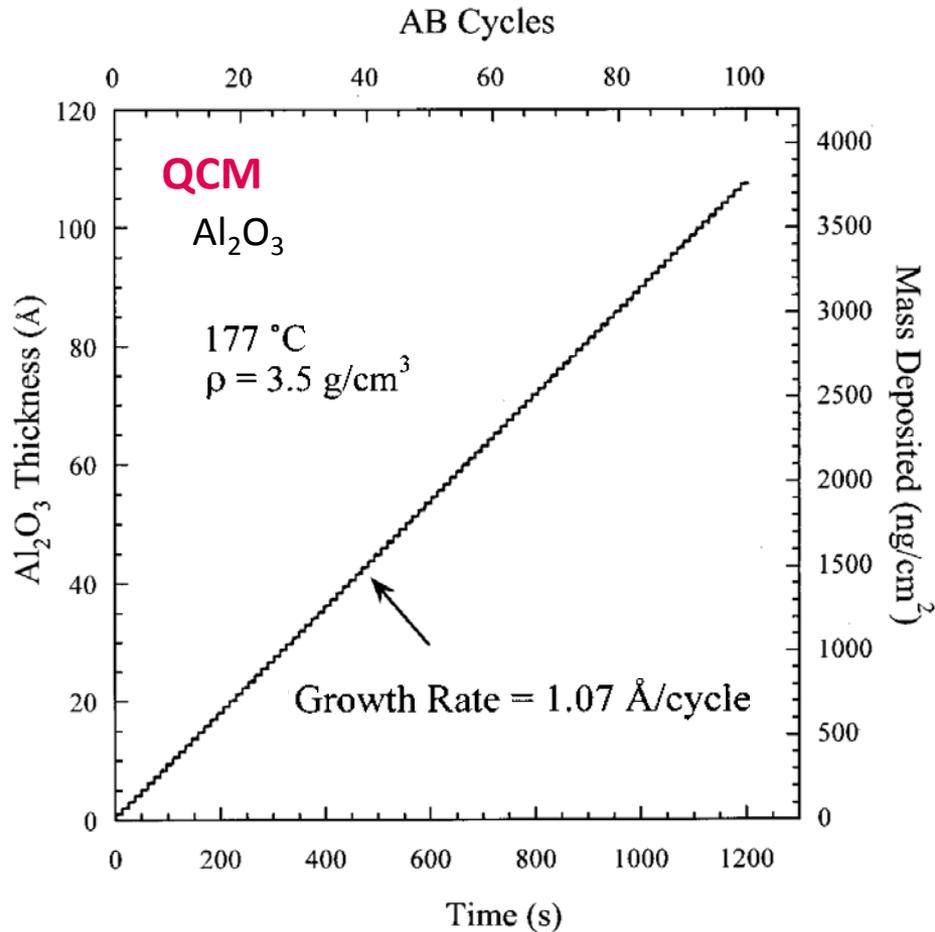
## COSTS



## Discussed **today**:

- Quartz crystal microbalance
- Spectroscopic ellipsometry
- Mass spectrometry
- Gas phase infrared spect.
- Surface infrared spect.
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- **Sum-frequency generation**
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- ...

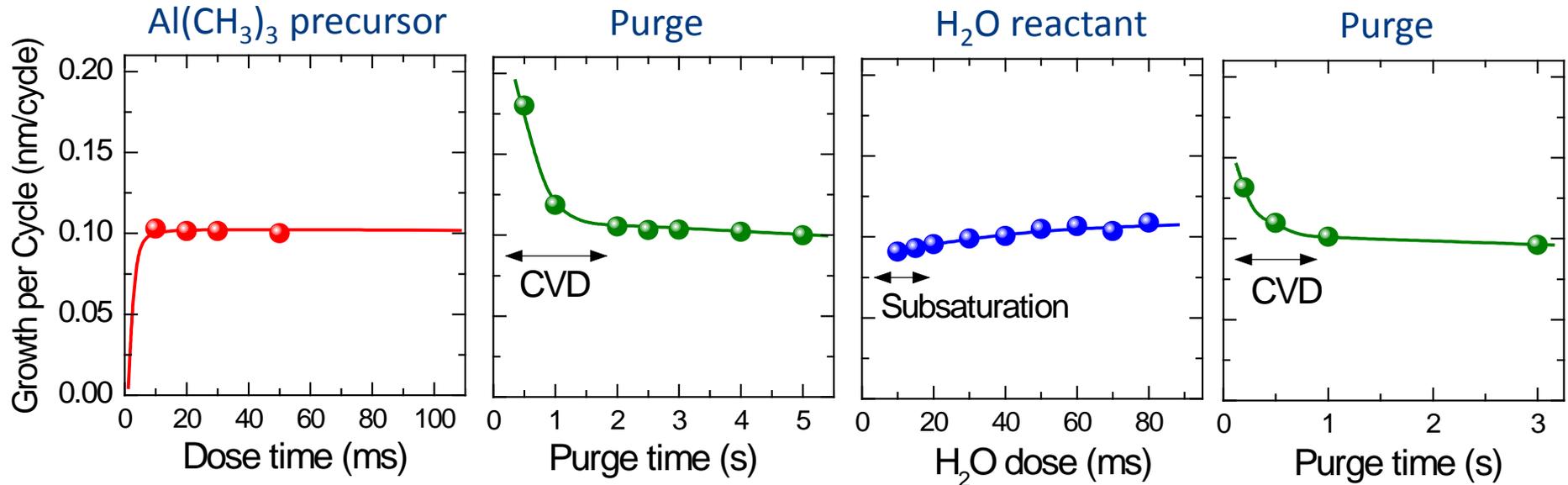
# Monitoring (linear) film growth



Material	Growth per cycle
$\text{Al}_2\text{O}_3$	1.2 Å (100 °C)
$\text{Ta}_2\text{O}_5$	0.80 Å (225 °C)
$\text{TiO}_2$	0.45 Å (200 °C)

# ALD saturation curves

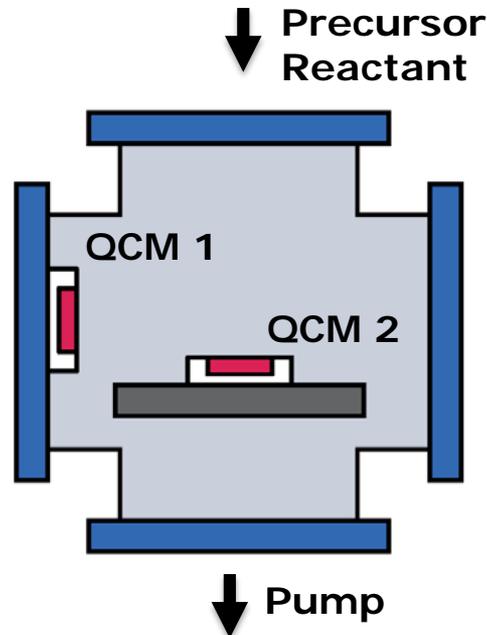
ALD of  $\text{Al}_2\text{O}_3$  from  $\text{Al}(\text{CH}_3)_3$  and  $\text{H}_2\text{O}$  (200 °C)



Vary one parameter while keeping other constant:

$\text{Al}(\text{CH}_3)_3$  – purge –  $\text{H}_2\text{O}$  – purge  
20 ms – 2 s – 40 ms – 1 s

# Quartz crystal microbalance (QCM)



QCM sensor = quartz crystal  
in resonator housing

## Measures mass variation of a quartz crystal resonator from its frequency change

- ▲ • Cheap device and relatively easy-to-implement on many reactors
- ▲ • Directly measures mass gain/loss in quantitative way
- ▲ • Very helpful for process development
- ▼ • Very sensitive to variations in pressure, gas flows and temperature

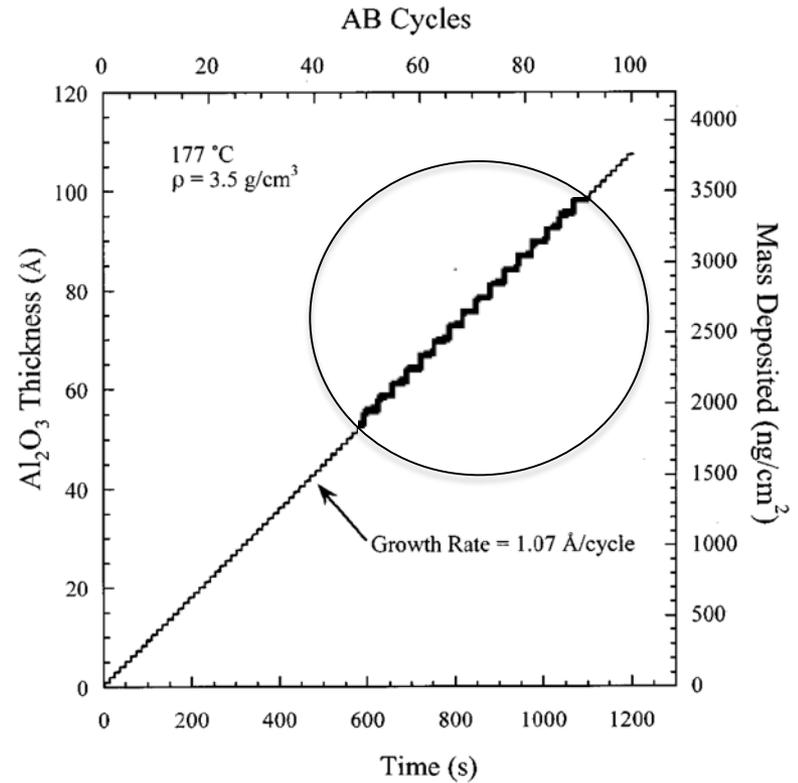
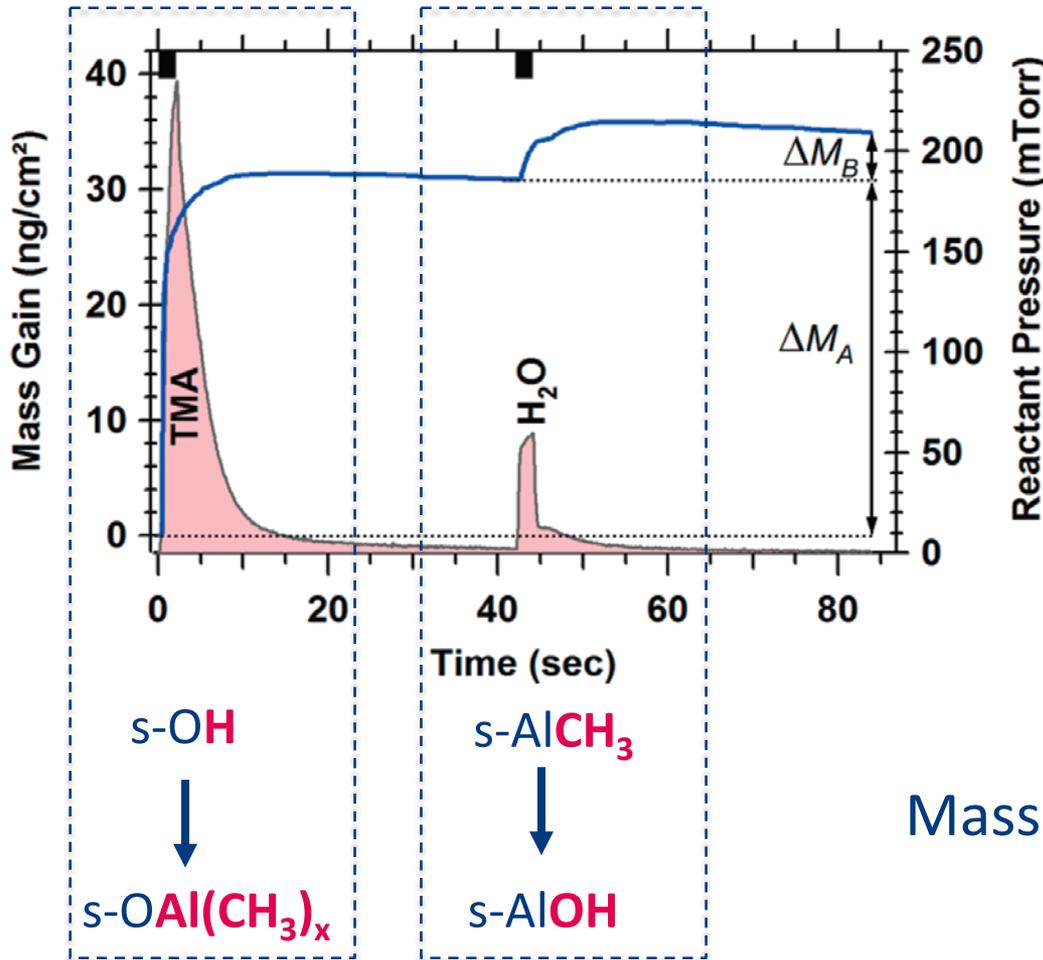
# Quartz crystal microbalance (QCM)



**Measures mass variation of a quartz crystal resonator from its frequency change**

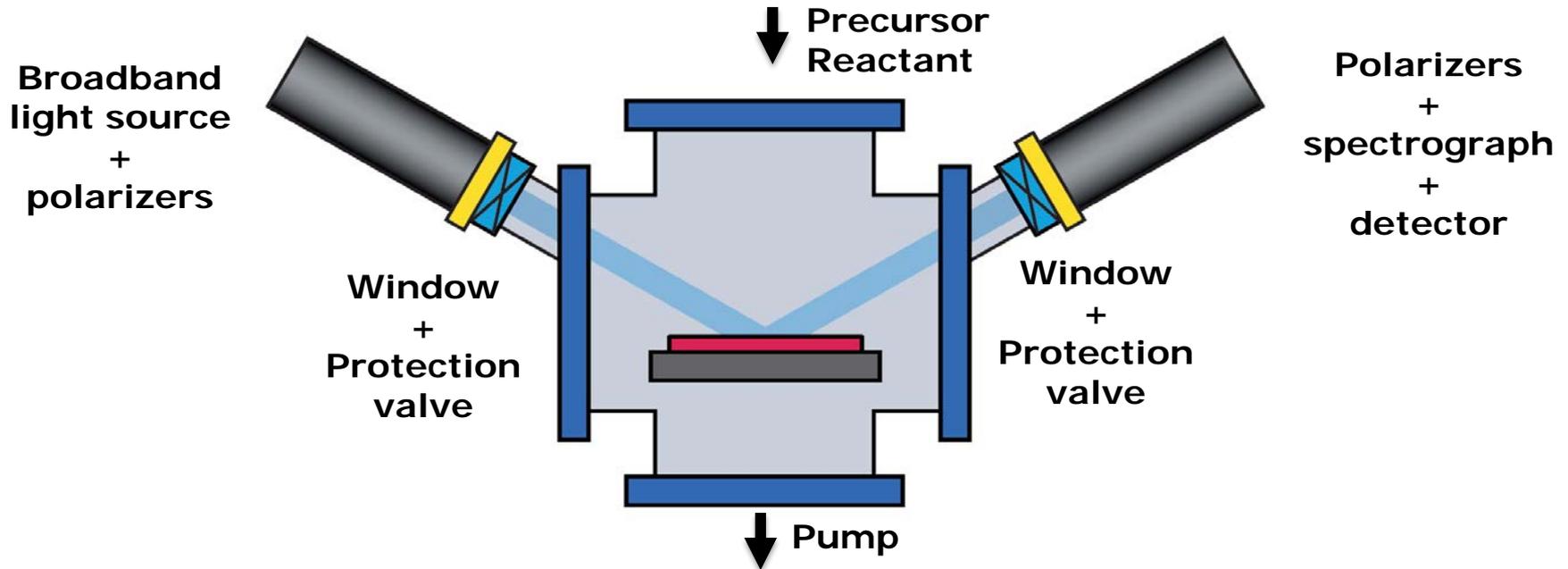
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- ▲ • Very helpful for process development
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# QCM – Monitoring mass gain ( $\text{Al}_2\text{O}_3$ )



Mass gain/loss can be monitored  
**per half-cycle**

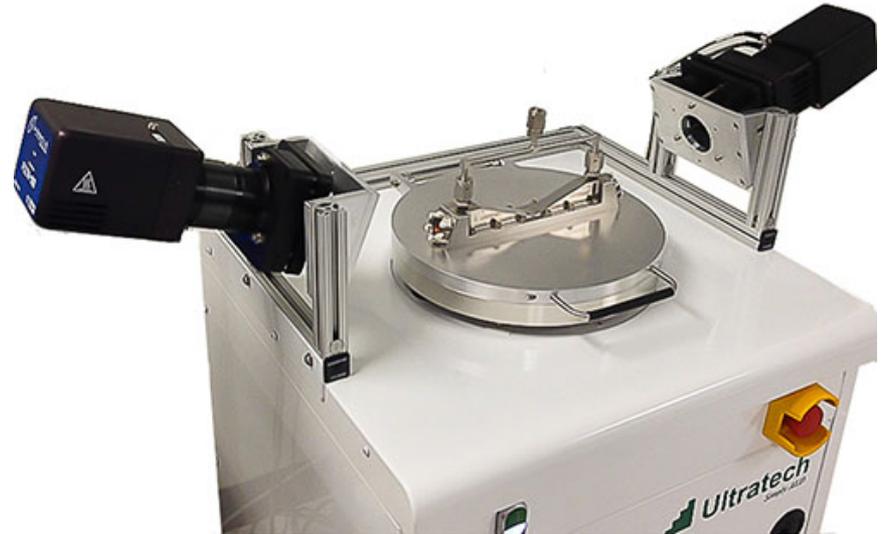
# Spectroscopic ellipsometry (SE)



## Measures change of polarization of light upon reflection (multiple wavelengths)

- ▲ • Directly measures thickness, very helpful for (fast) process development
- ▲ • Yields also insight into many other material properties (optical/electrical)
- ▼ • Optical modelling can be challenging for some layers/materials
- ▼ • Rather expensive and requires special ports for optical access

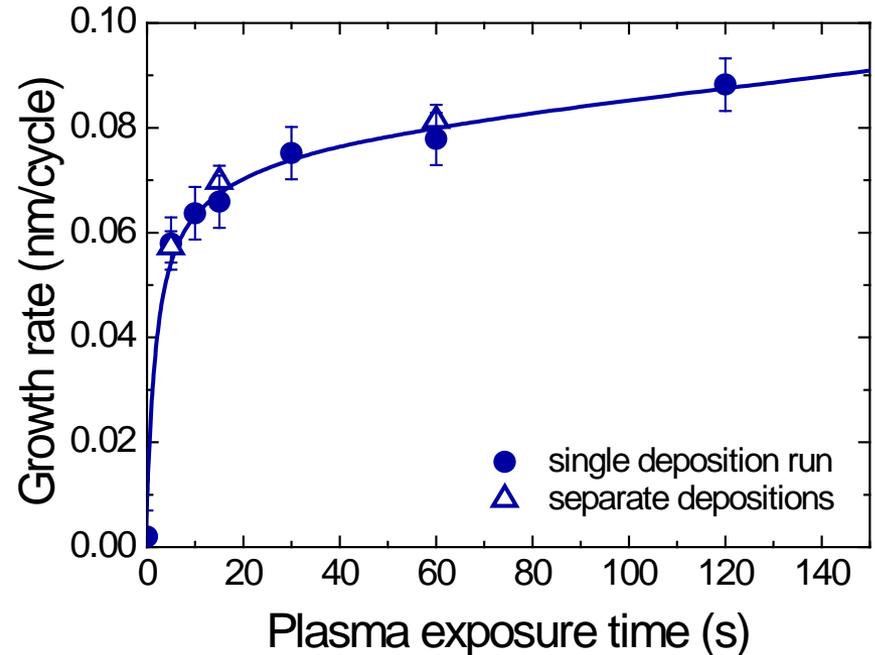
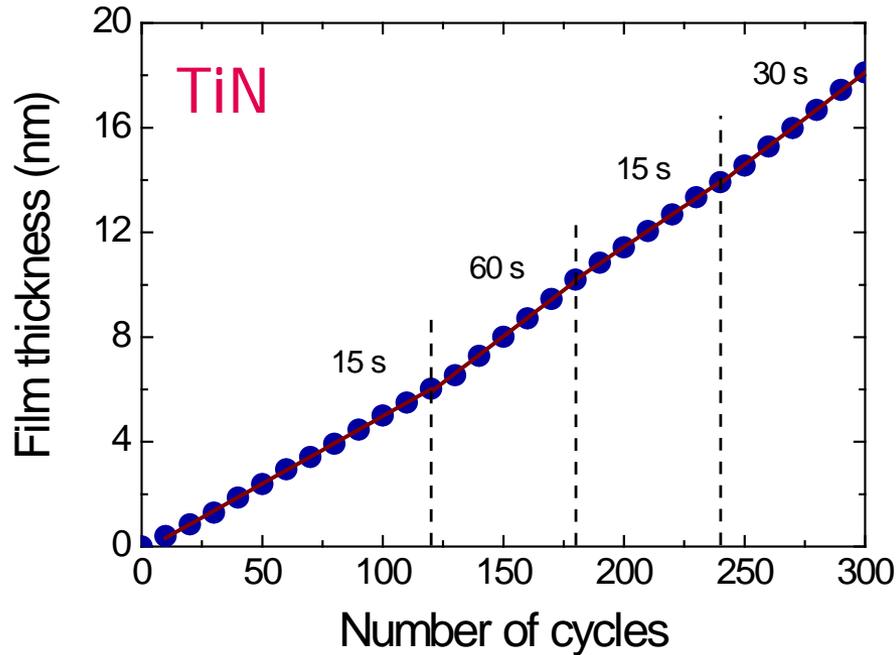
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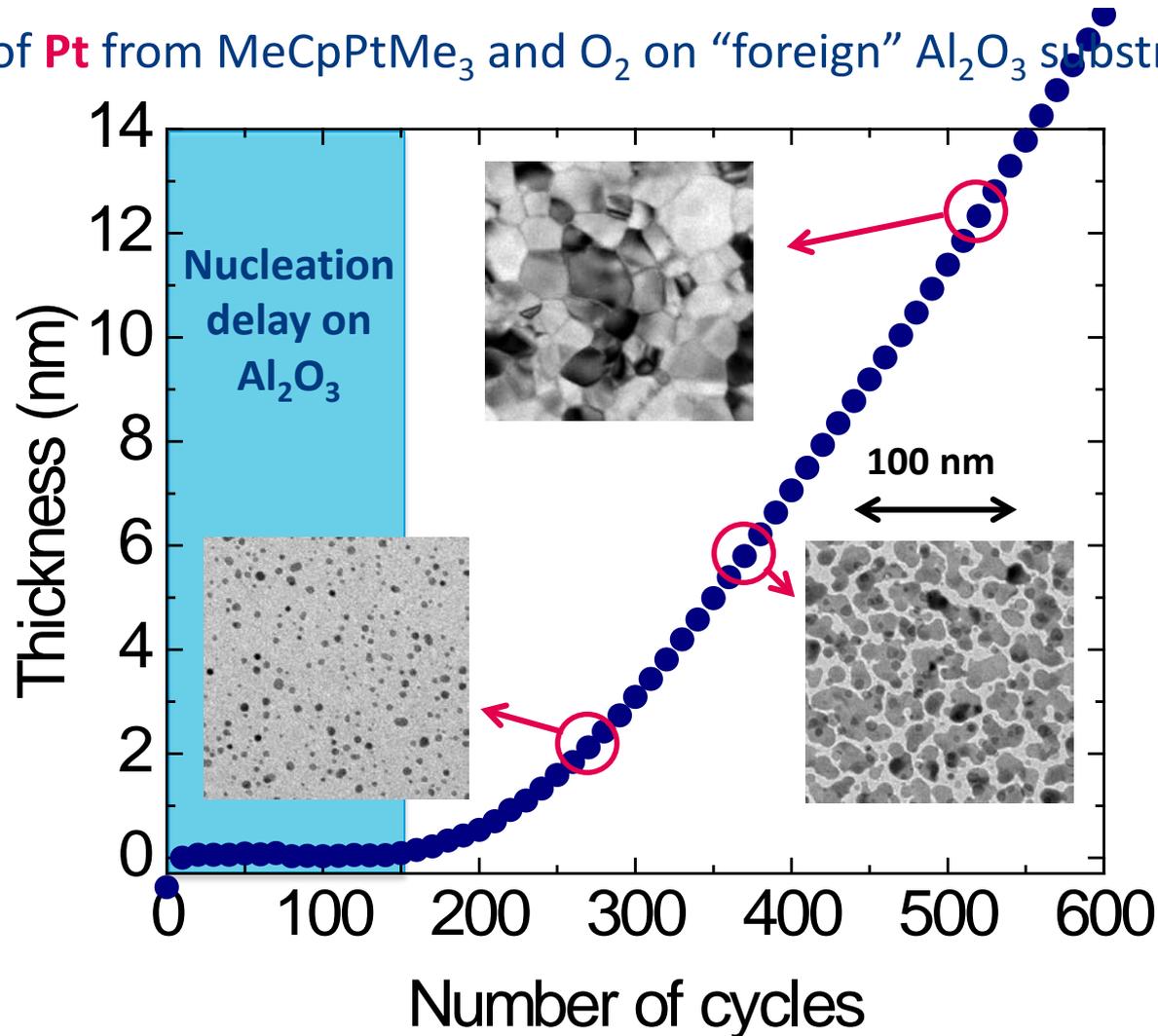
# Spectroscopic ellipsometry – Saturation (TiN)



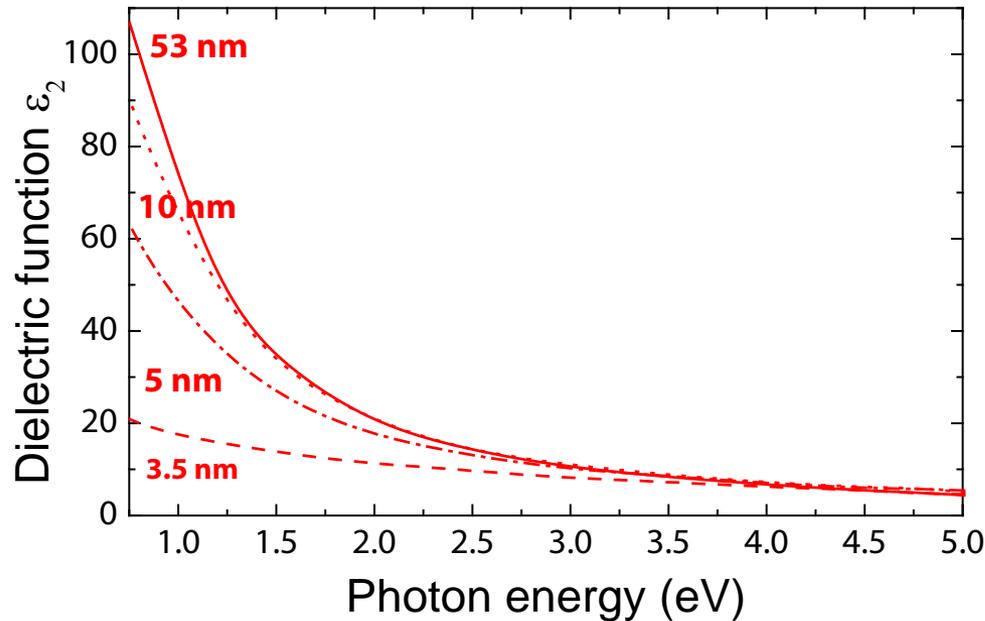
Monitor film thickness while changing precursor/reactant dosing time provides a **fast method to determine saturation curves**

# Spectroscopic ellipsometry – Nucleation (Pt)

ALD of **Pt** from MeCpPtMe<sub>3</sub> and O<sub>2</sub> on “foreign” Al<sub>2</sub>O<sub>3</sub> substrate (300 °C)



# Spectroscopic ellipsometry – Resistivity (Pt)



Imaginary part of dielectric function  $\epsilon$

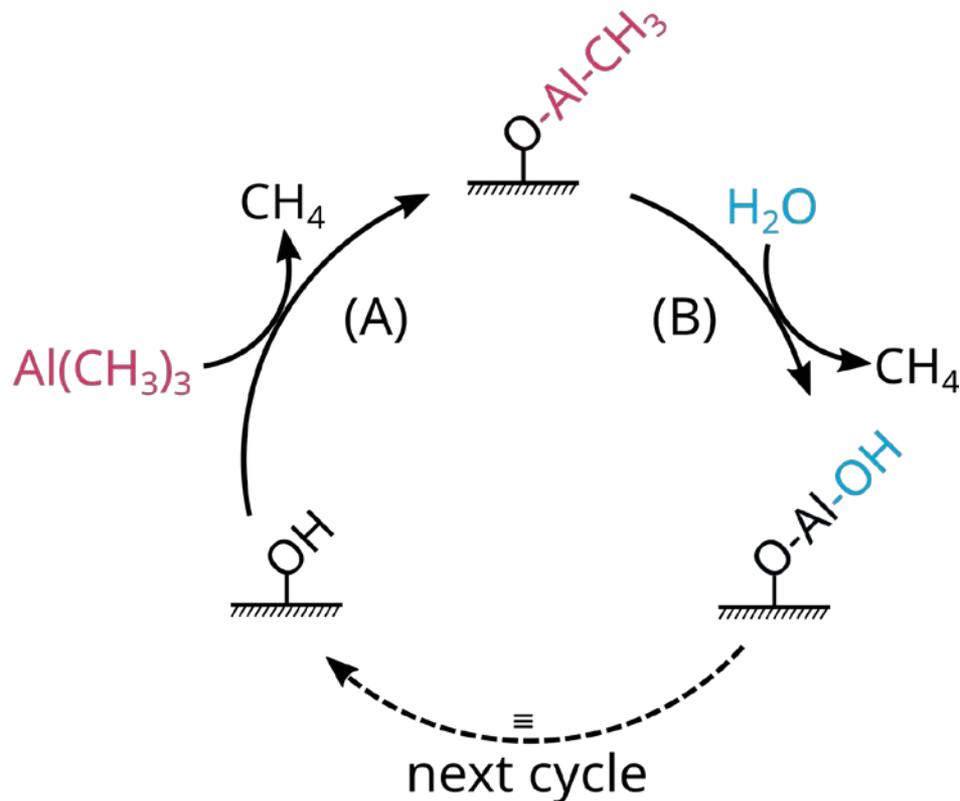
$$\epsilon_2(\omega) = \epsilon_\infty - \frac{\omega_p^2}{\omega^2 - i\omega/\tau_D} + \sum_{j=1}^n \frac{f_j \omega_p^2}{\omega_{0j}^2 - \omega^2 + i\gamma_j \omega}$$

Drude  
term  
(resistivity)

Lorentz  
terms

	Optical resistivity ( $\mu\Omega$ cm)	FPP resistivity ( $\mu\Omega$ cm)	Bulk resistivity ( $\mu\Omega$ cm)
Pt (53 nm)	12.6	$13.0 \pm 0.2$	10.4
Ru (90 nm)	32.8	$18.0 \pm 0.6$	6.7
Pd (42 nm)	67.5	$67 \pm 1$	10.5

# ALD of Al<sub>2</sub>O<sub>3</sub> [Case study]



## Prototypical ALD process

Precursor: Al(CH<sub>3</sub>)<sub>3</sub>

Reactant: H<sub>2</sub>O

Temperature: 25-400 °C

## Simplified reaction scheme:

### A - 1<sup>st</sup> Half Cycle

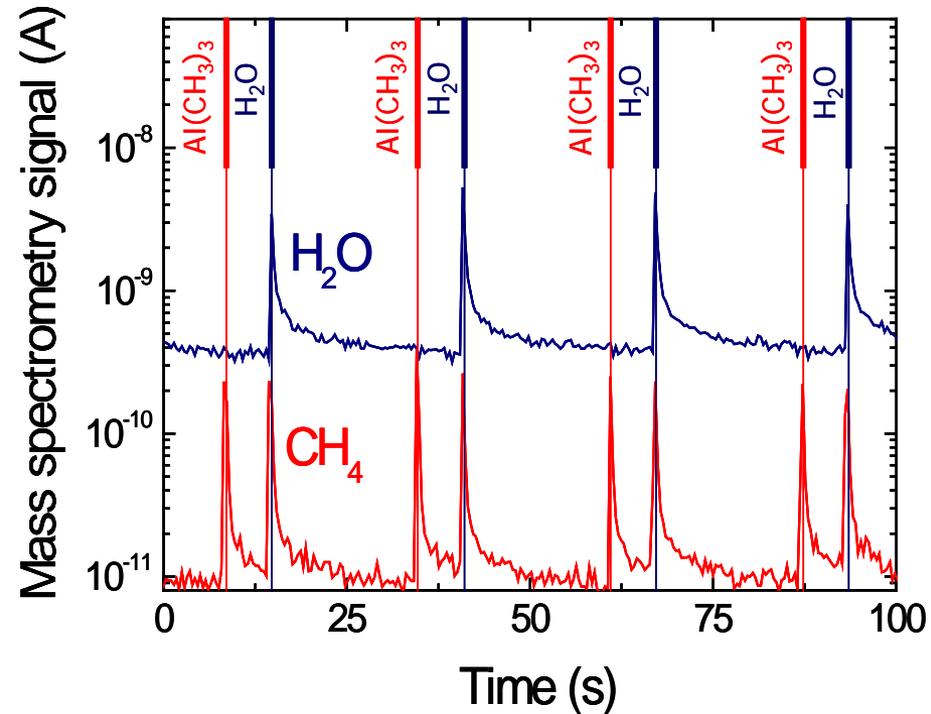
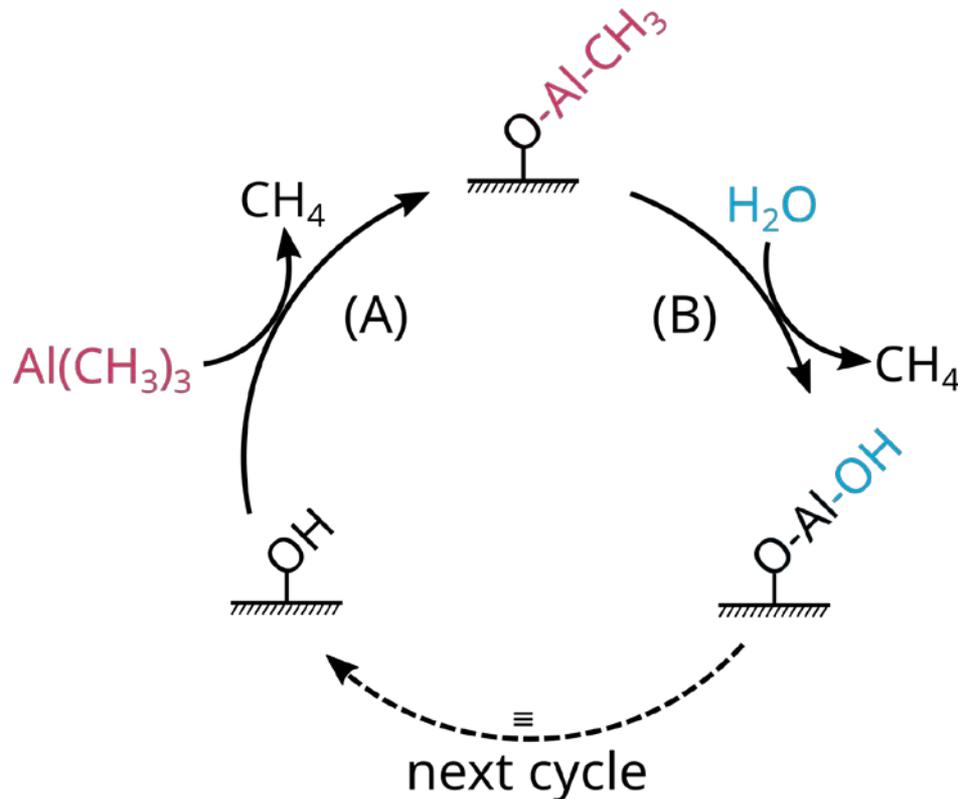


### B - 2<sup>nd</sup> Half Cycle



# Mass spectrometry — Reaction products ( $\text{Al}_2\text{O}_3$ )

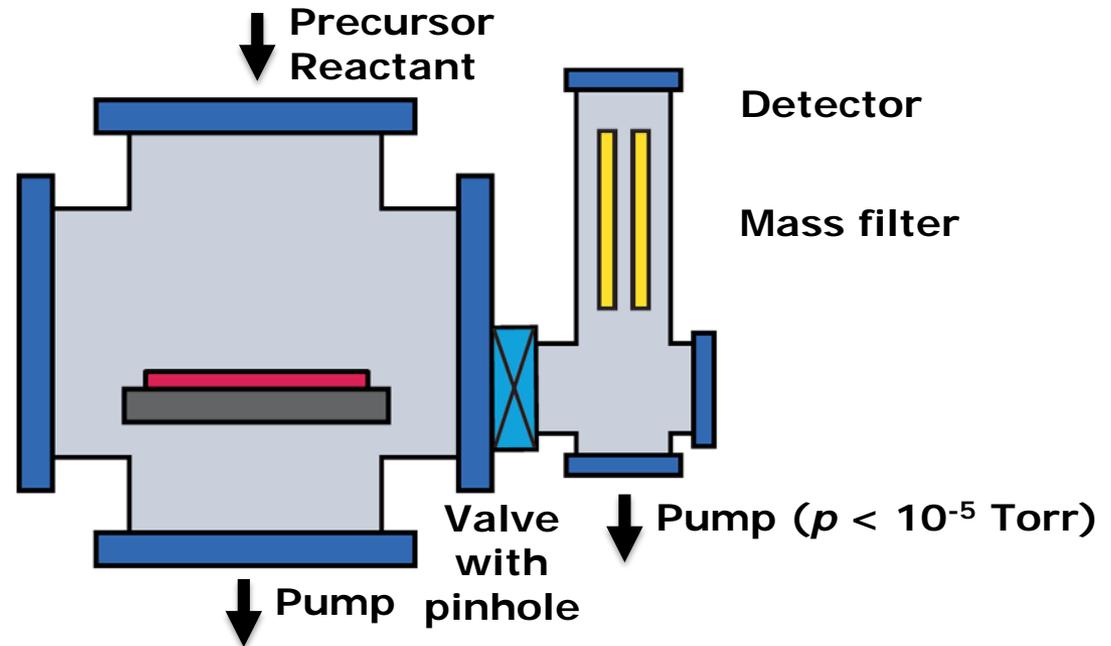
Gas phase **reaction products**



$\text{Al}(\text{CH}_3)_3$  dosing:  **$\text{CH}_4$**

$\text{H}_2\text{O}$  dosing:  **$\text{CH}_4$**

# Quadrupole mass spectrometry (QMS)



## Ionization of gas extracted from the reactor & mass filtering of the ions

- ▲ • Easy-to-implement on all types of reactors (with differential pumping)
- ▲ • Wide range of species can be detected (but heavy masses difficult)
- ▲ ▼ • All reaction products measured (not only from substrate)
- ▼ • QMS cracks molecules into fragments complicating data interpretation

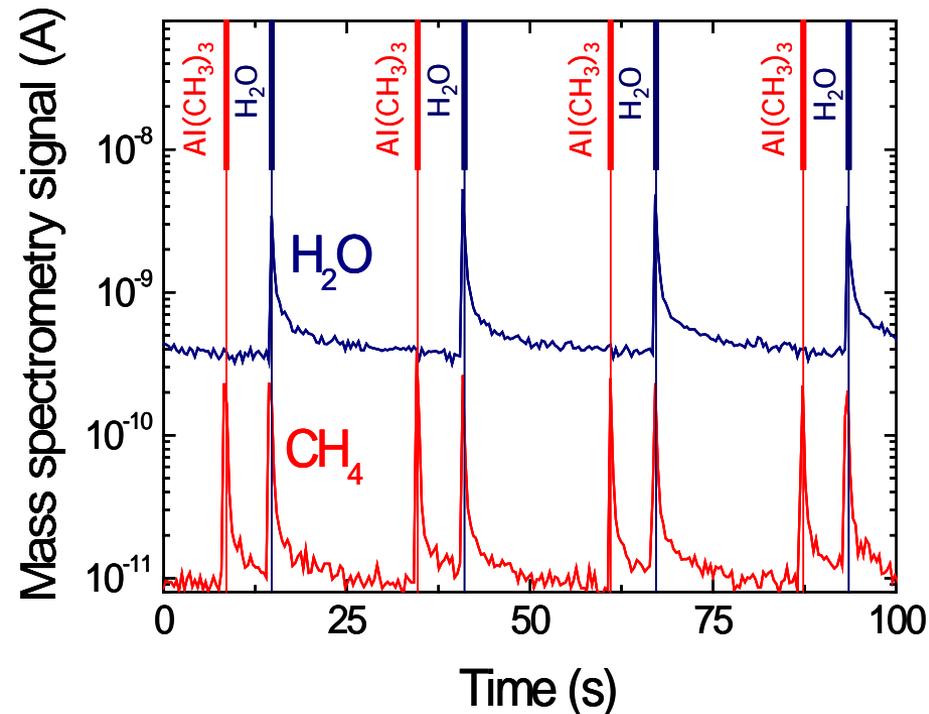
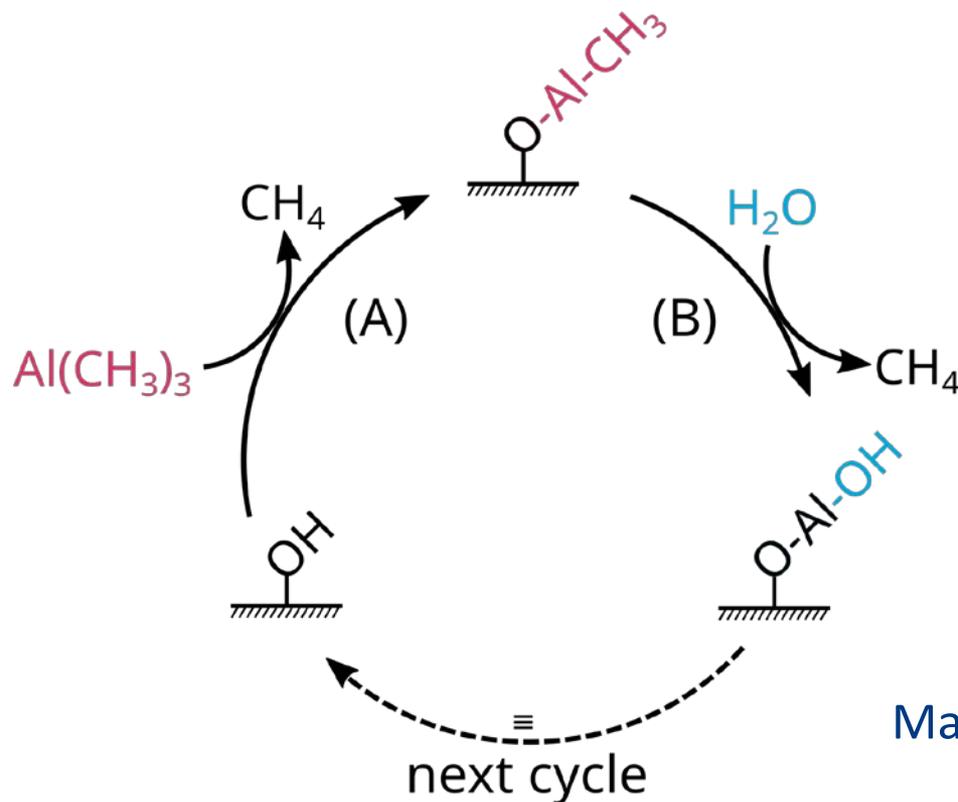
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# Mass spectrometry — Reaction products ( $\text{Al}_2\text{O}_3$ )

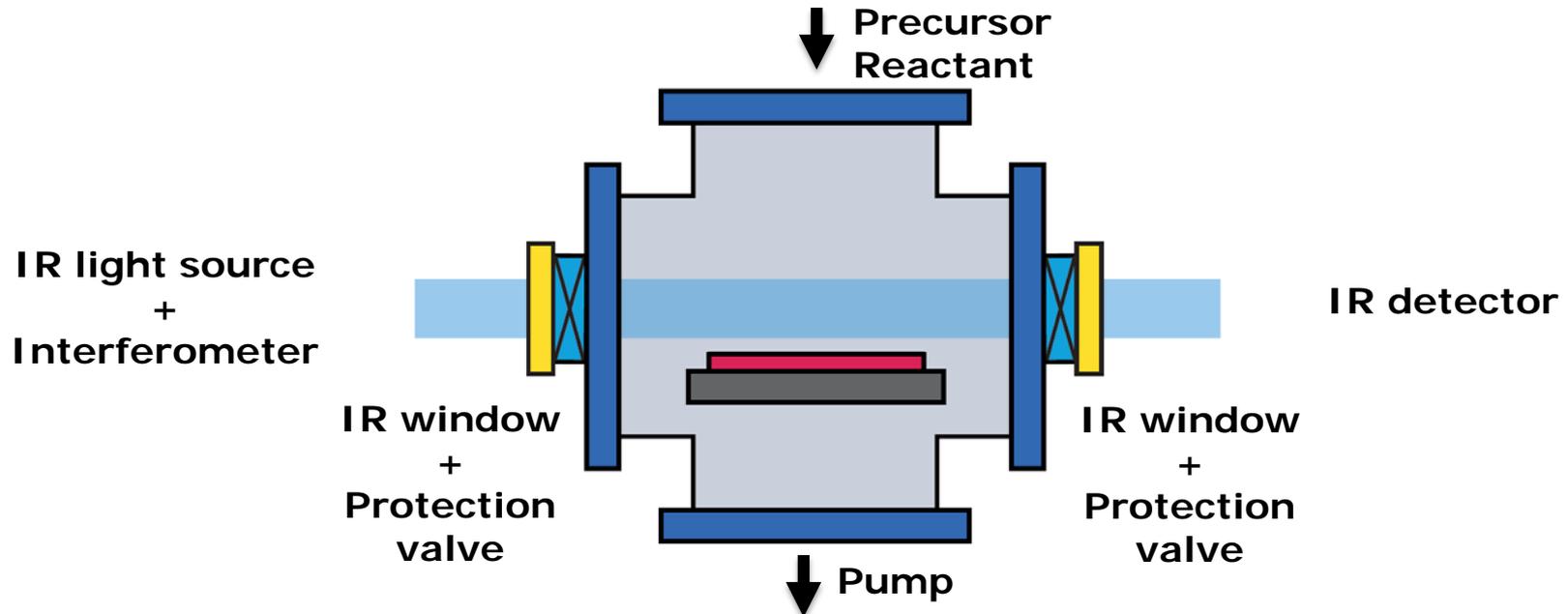


Mass spectrometry probes **mass/charge ratios**

$\text{CH}_4$  probed at **16 ( $\text{CH}_4^+$ )**; 15 ( $\text{CH}_3^+$ ), etc.

$\text{H}_2\text{O}$  probed at 18 ( $\text{H}_2\text{O}^+$ ); 17 ( $\text{OH}^+$ ); **16 ( $\text{O}^+$ )**

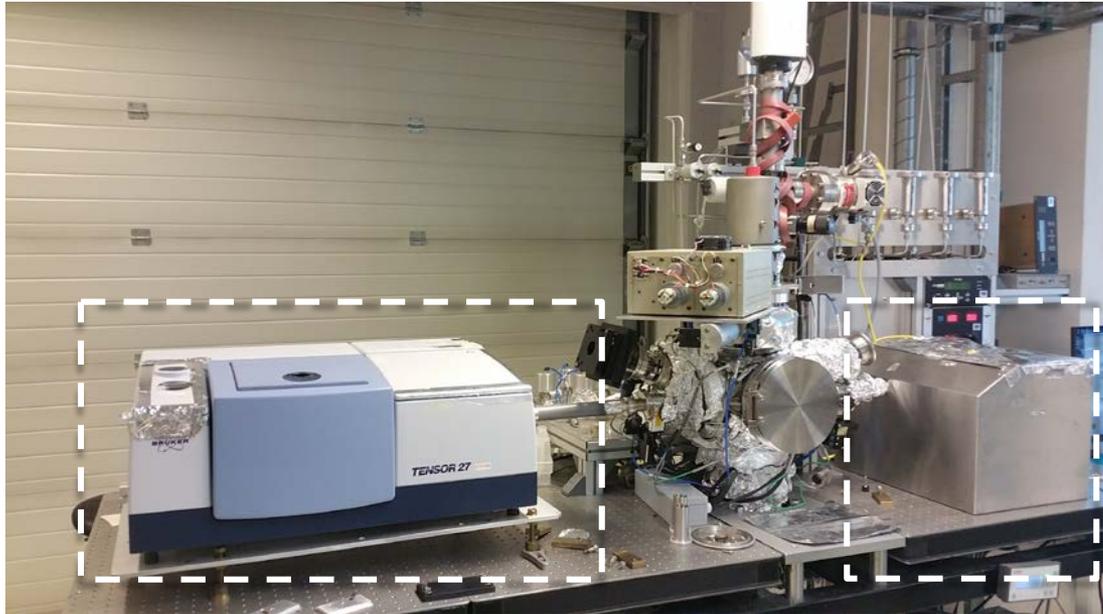
# Gas-phase infrared spectroscopy (FTIR)



## Absorption of infrared light (from FTIR interferometer) by rovibrational transitions

- ▲ . Calibration is quite straightforward to yield absolute densities
- ▲▼ . High sensitivity for certain species but not all species can be detected
- ▲▼ . All reaction products measured (not only from substrate)
- ▼ . Confinement of reaction products might be necessary for sufficient S/N ratio

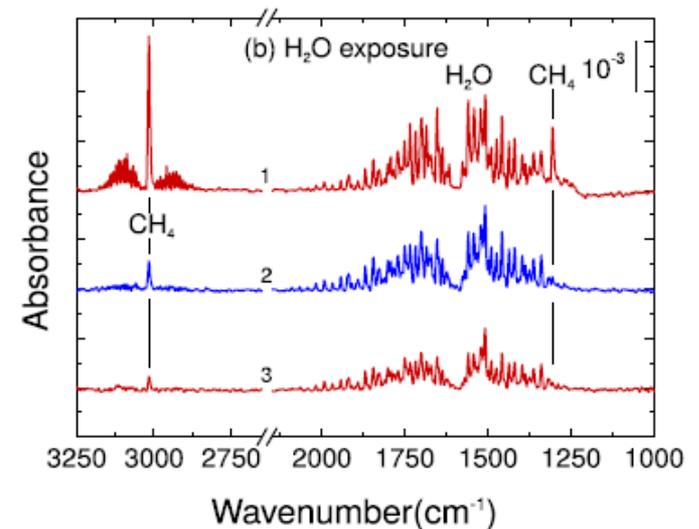
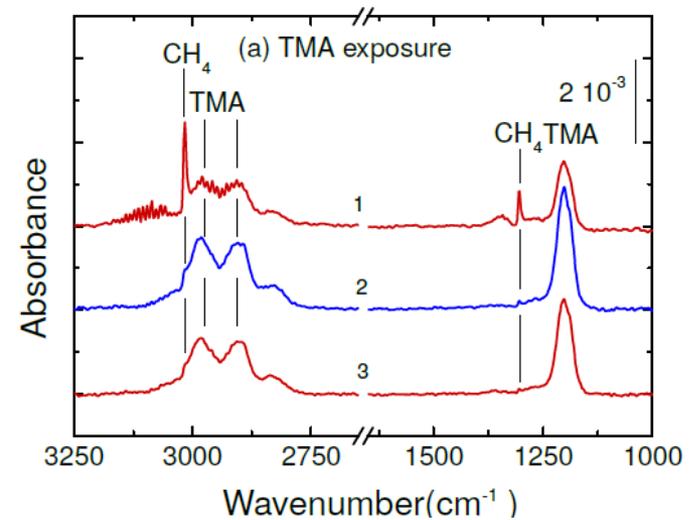
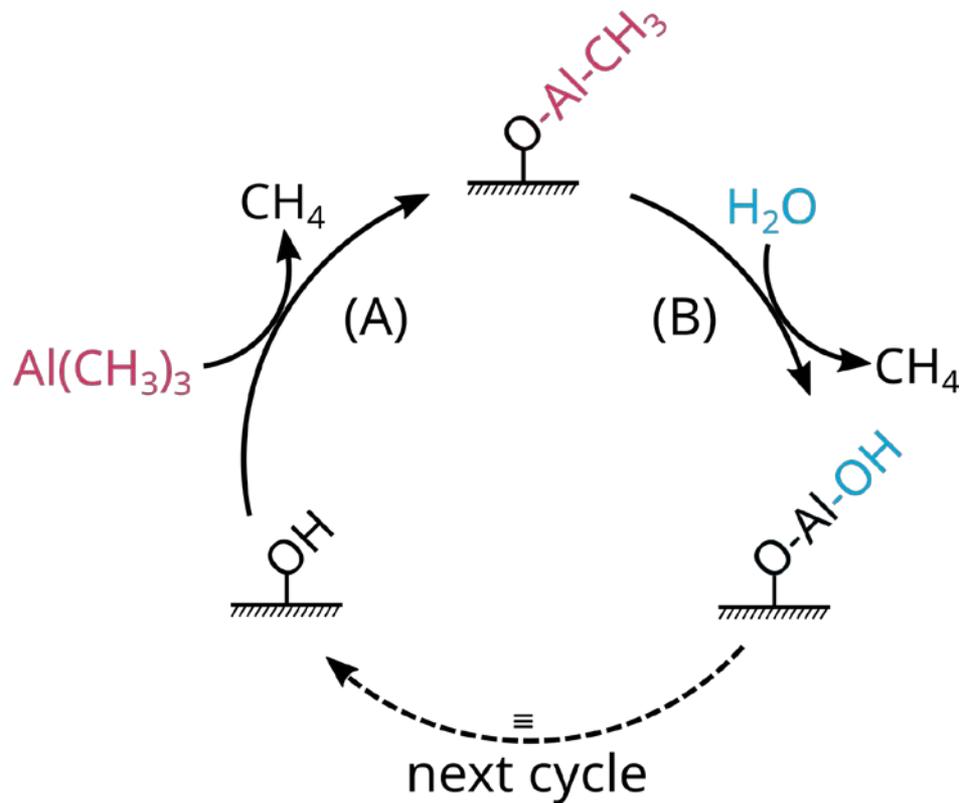
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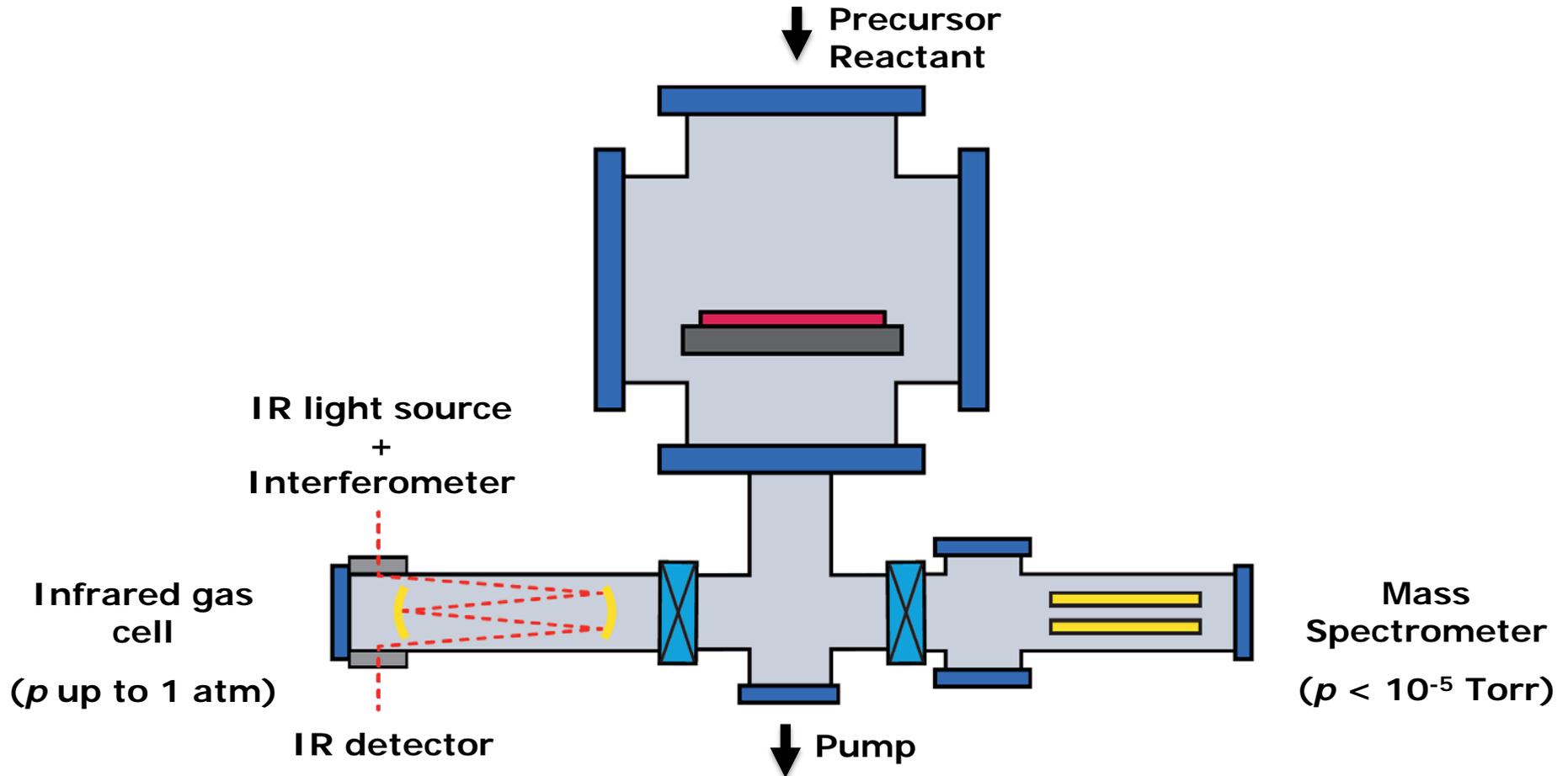
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# Gas-phase FTIR — Reaction products ( $\text{Al}_2\text{O}_3$ )

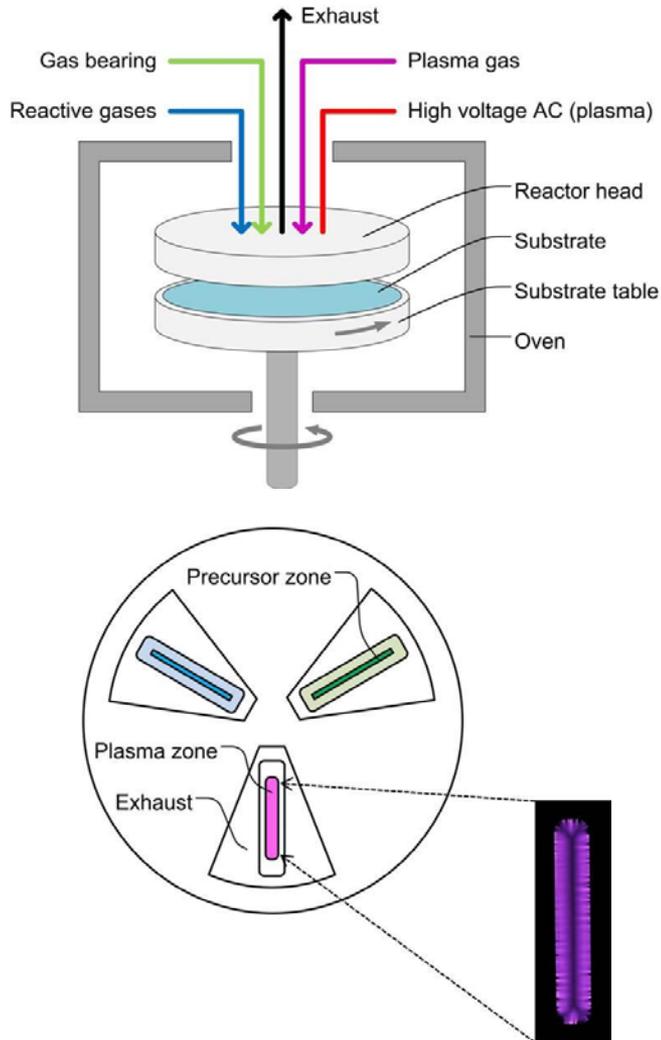


# QMS and gas-phase FTIR installed in exhaust

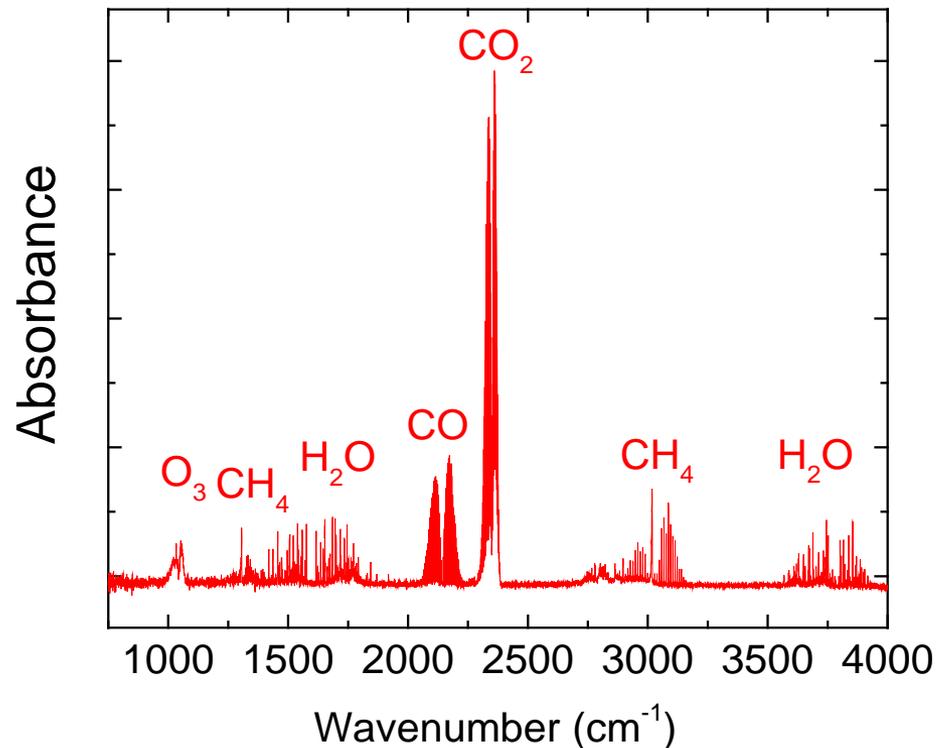


Can quite easily be implemented in **industrial (spatial)** ALD equipment

# Gas-phase FTIR in exhaust of spatial ALD setup

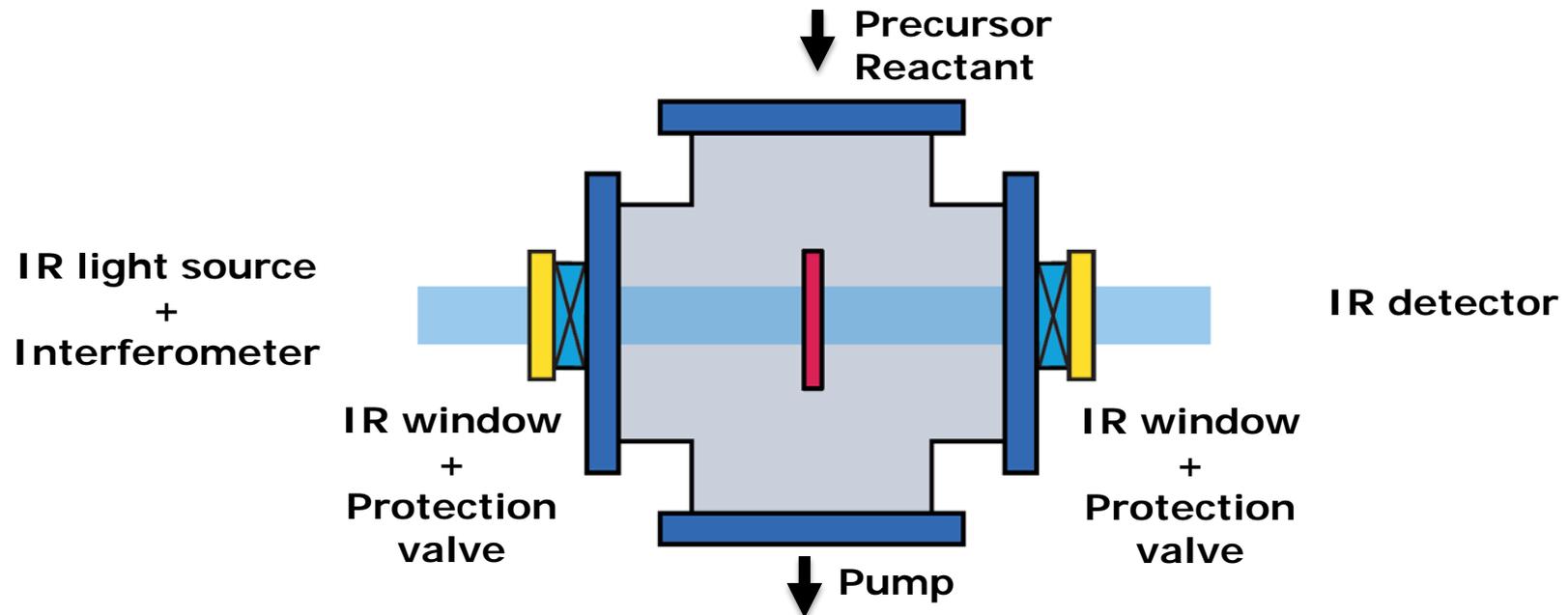


Spectrum of O<sub>2</sub> plasma reactant step during plasma-assisted spatial ALD of Al<sub>2</sub>O<sub>3</sub>



Reaction products:  
O<sub>3</sub>, combustion products and CH<sub>4</sub>

# Surface infrared spectroscopy (FTIR)

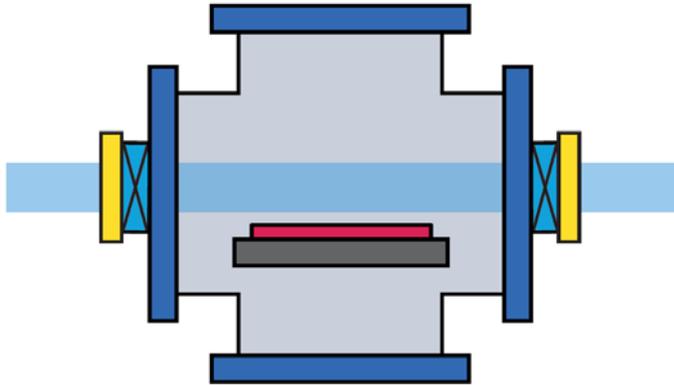


## Absorption of infrared light by vibrational transitions by (surface) groups

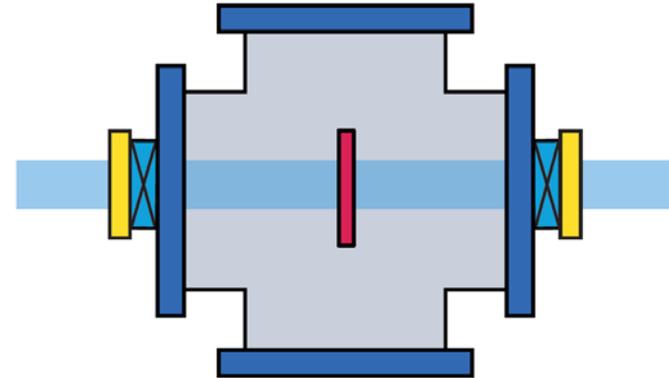
- ▲ • Direct measurement of surface groups created, removed or incorporated
- ▲▼ • Probes only surface groups which are changing every (half-)cycle
- ▼ • Poor S/N ratio for some species – long integration times required
- ▼ • Requires dedicated reactor with optical access and IR-transparent substrate

# Various configurations infrared spectroscopy

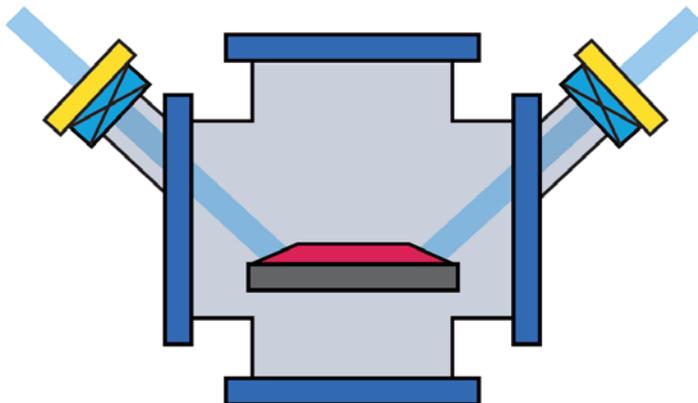
**Gas phase species**



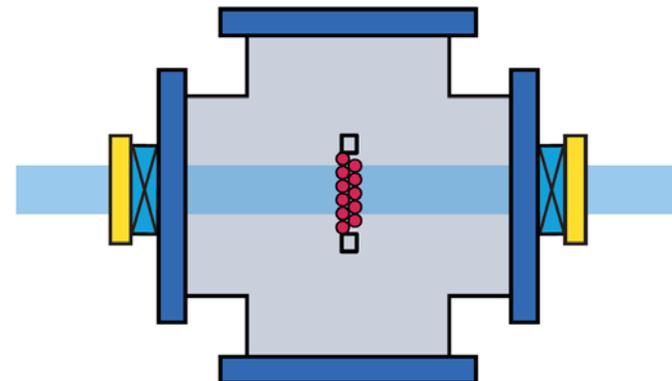
**Surface species - wafer**



**Surface species – ATR element**  
(multiple reflections at surface)



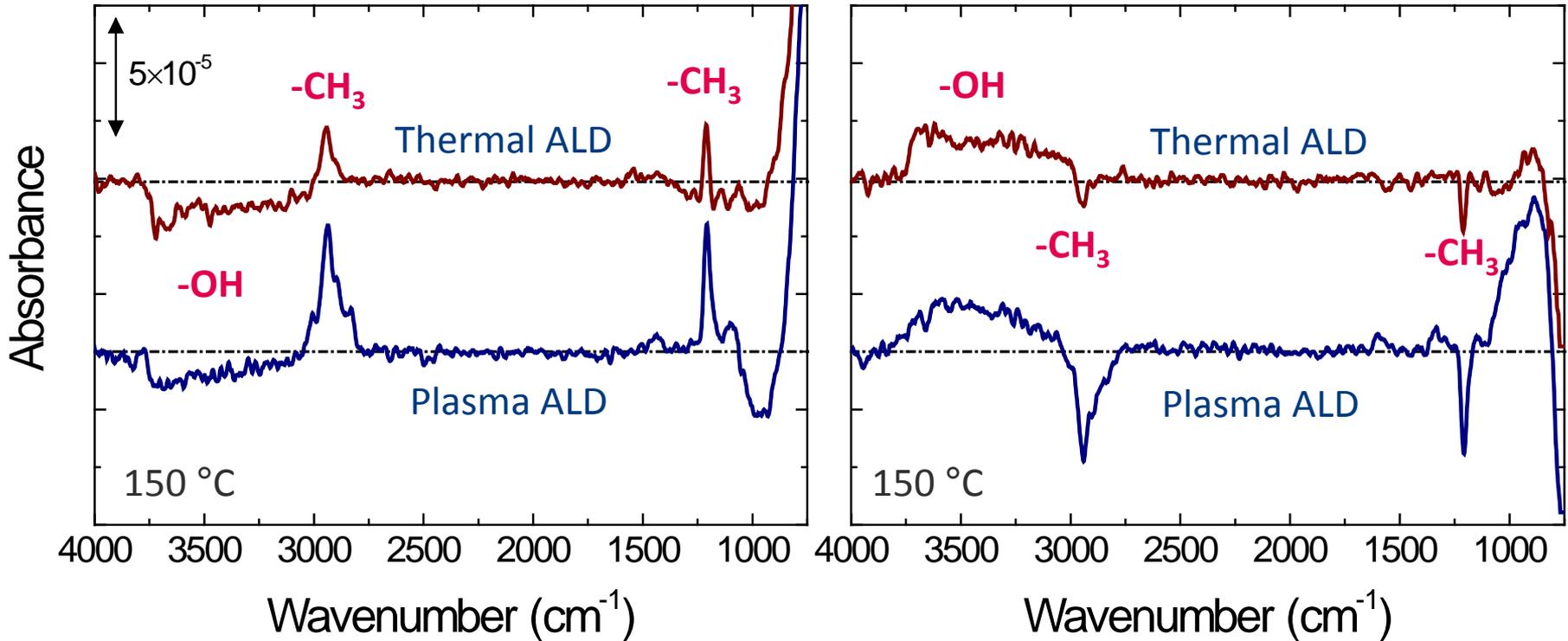
**Surface species – particles**  
(enlarged surface area by particles)



# Surface FTIR – Surface groups (Al<sub>2</sub>O<sub>3</sub>)

Al(CH<sub>3</sub>)<sub>3</sub>

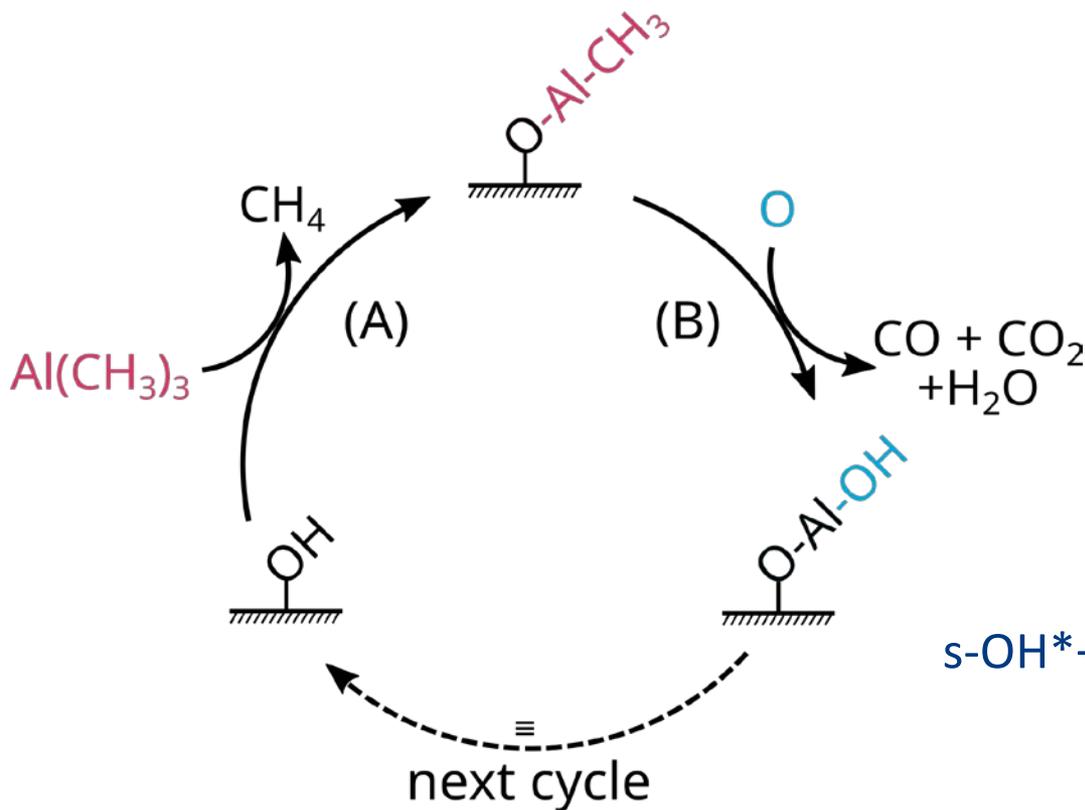
H<sub>2</sub>O or O<sub>2</sub> plasma



**Differential spectra:** show changes per half cycle

**-CH<sub>3</sub>** and **-OH** are surface groups for both thermal and plasma ALD

# Plasma-enhanced ALD of Al<sub>2</sub>O<sub>3</sub> [Case study]



Precursor: Al(CH<sub>3</sub>)<sub>3</sub>

Reactant: O<sub>2</sub> plasma

Temperature: 25-400 °C

**Simplified reaction scheme:**

**A - 1<sup>st</sup> Half Cycle**



**B - 2<sup>nd</sup> Half Cycle**



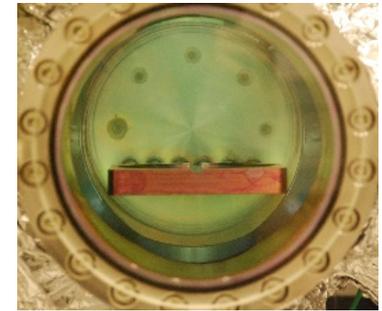
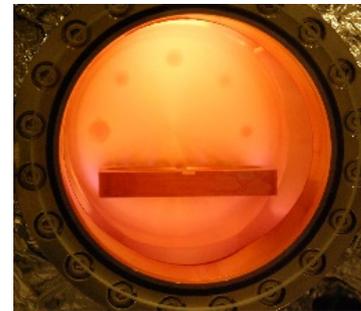
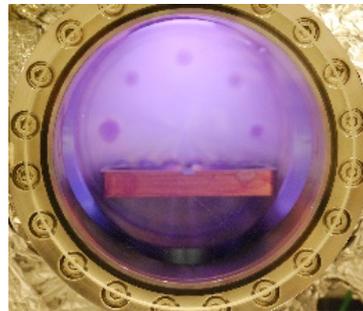
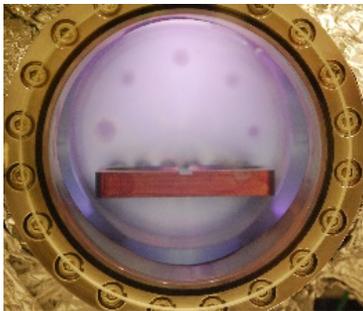
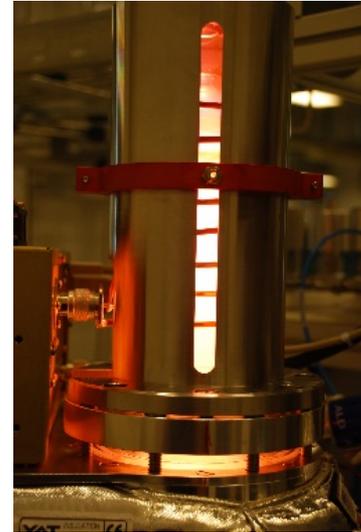
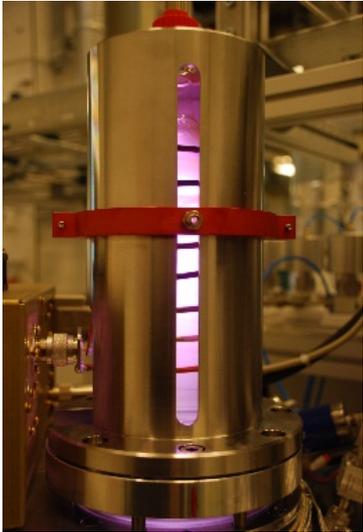
# Plasma radiation – feed gas dependent

Ar

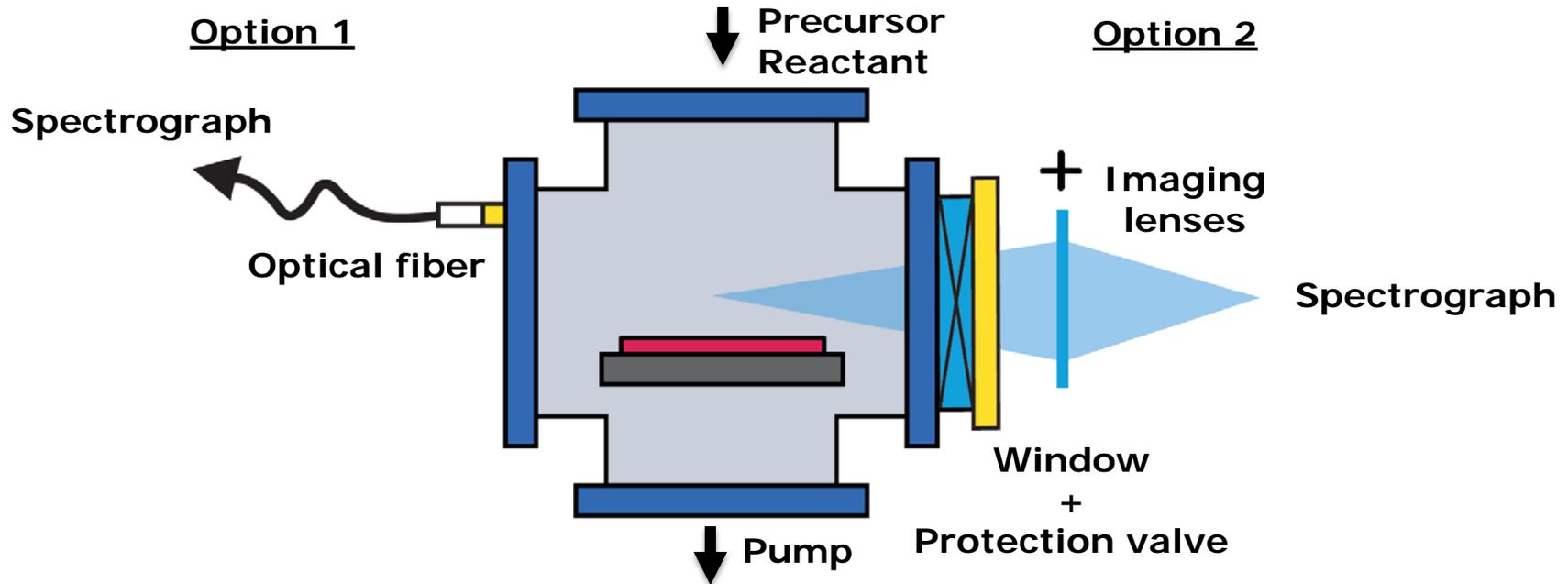
H<sub>2</sub>

N<sub>2</sub>

O<sub>2</sub>



# Optical emission spectroscopy (OES)



## Measures (visible) radiation from excited species decaying to lower levels

- ▲ • Ideally suited for process monitoring of plasma-based processes
- ▲ • Extremely easy to implement & cheap
- ▼ • Yields only information about excited species – not ground state species
- ▼ • Typically yields very indirect and qualitative information

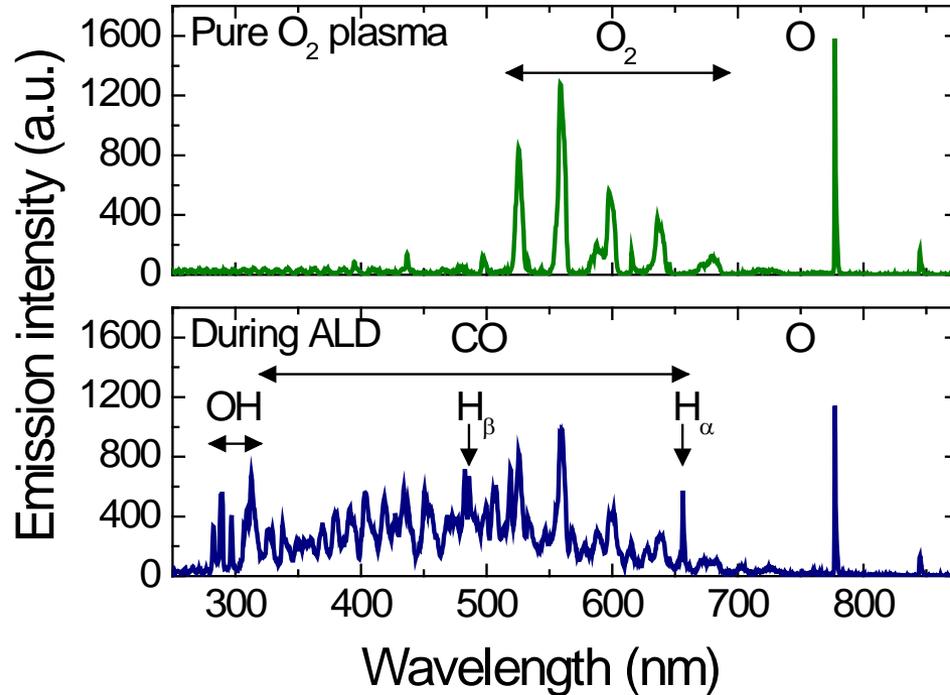
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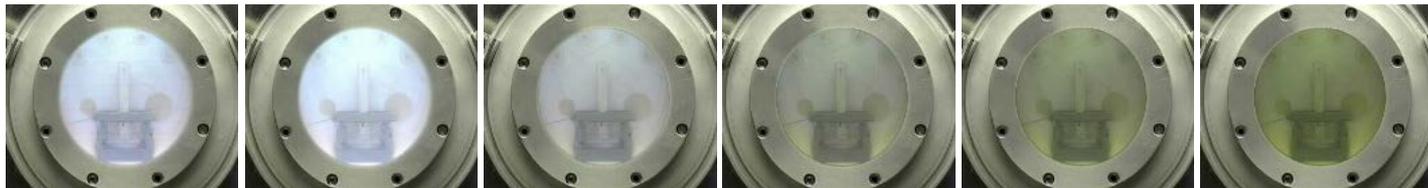
# Optical emission spectroscopy – Plasma (Al<sub>2</sub>O<sub>3</sub>)



## Plasma half-cycle

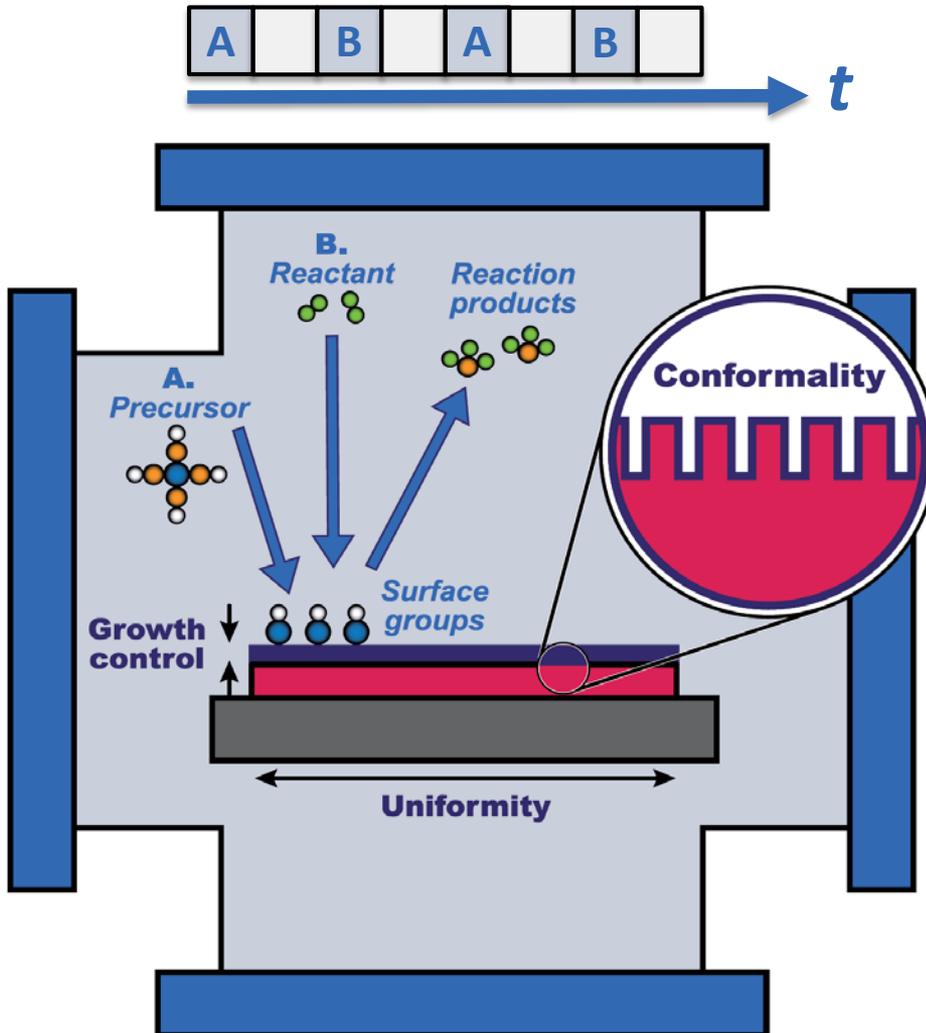


Plasma is “**disturbed**”  
by reaction products



-t: 0 s — 0.4 s — 0.8 s — 1.2 s — 1.6 s — 2.0 s →

# Atomic layer deposition (ALD)



Discussed **next**:

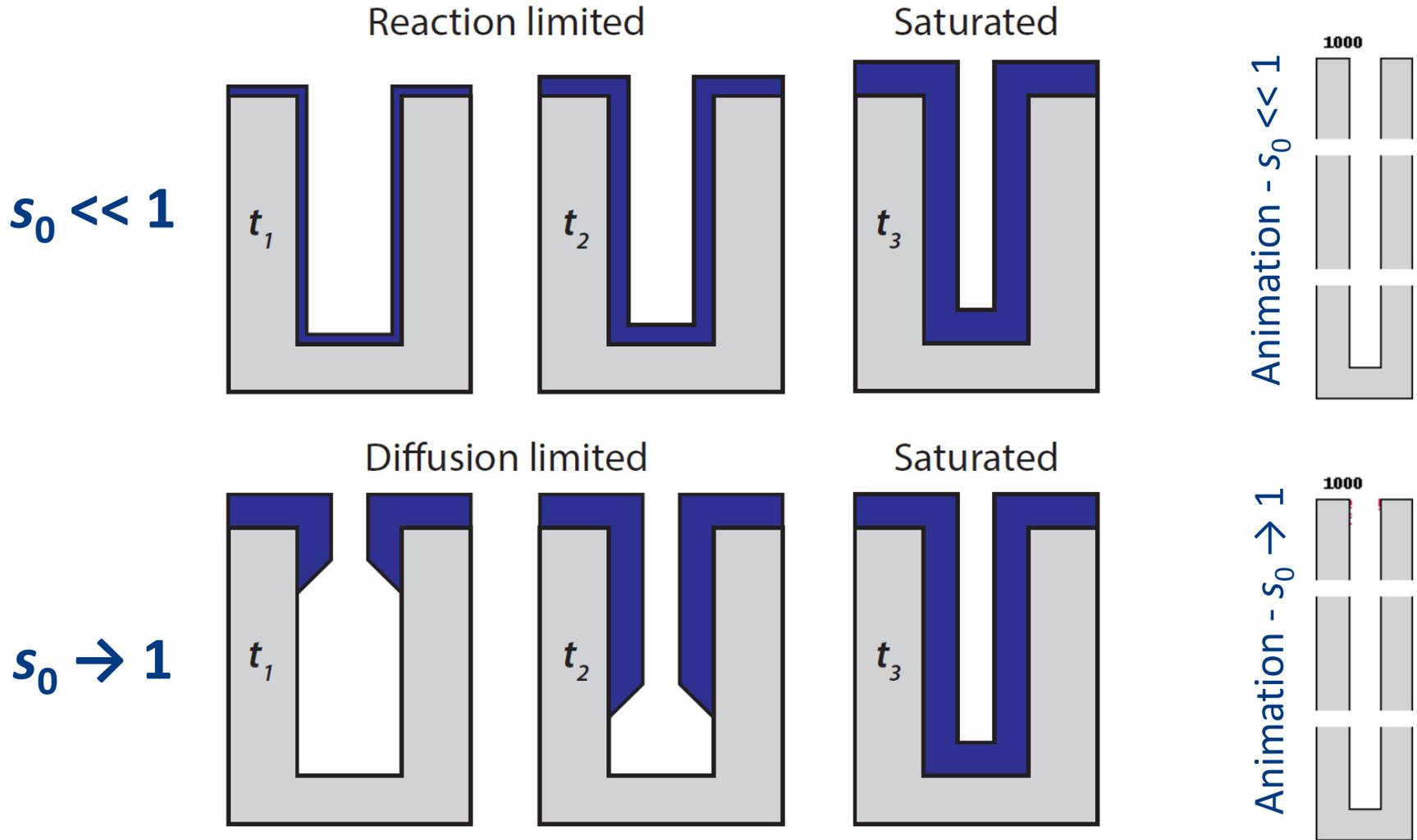
ALD merits:

- **Conformality**
- **Uniformity**
- **Growth control**

Advanced methods:

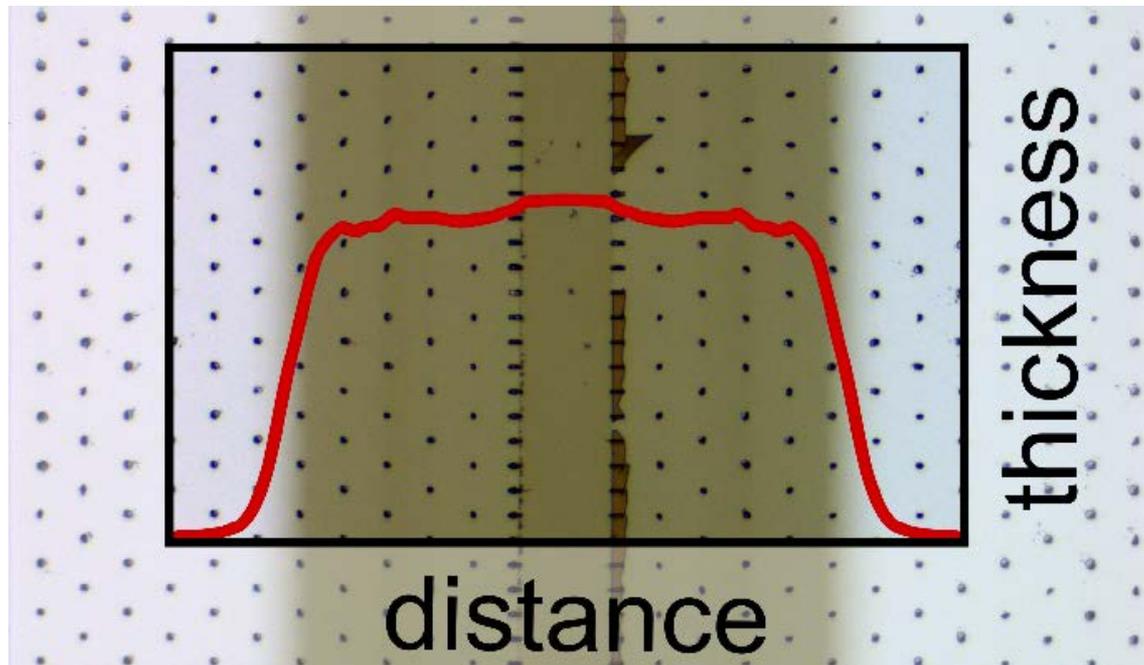
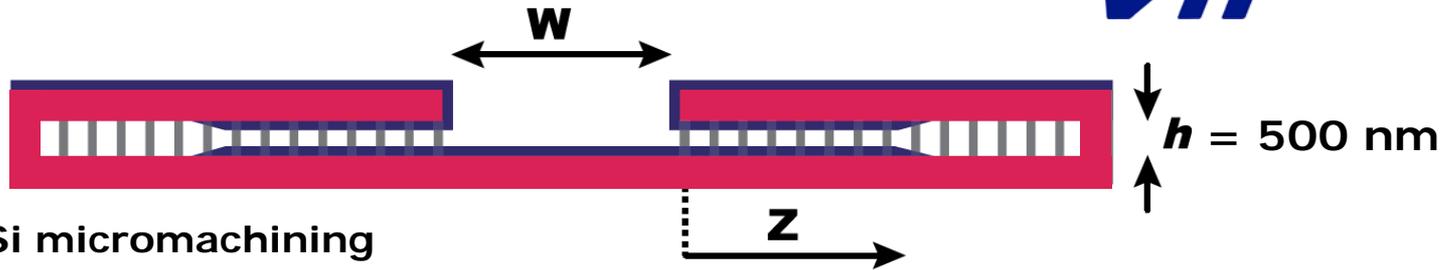
- **Sum-frequency generation**
- **Adsorption calorimetry**

# Conformality – Reaction- vs. diffusion-limited



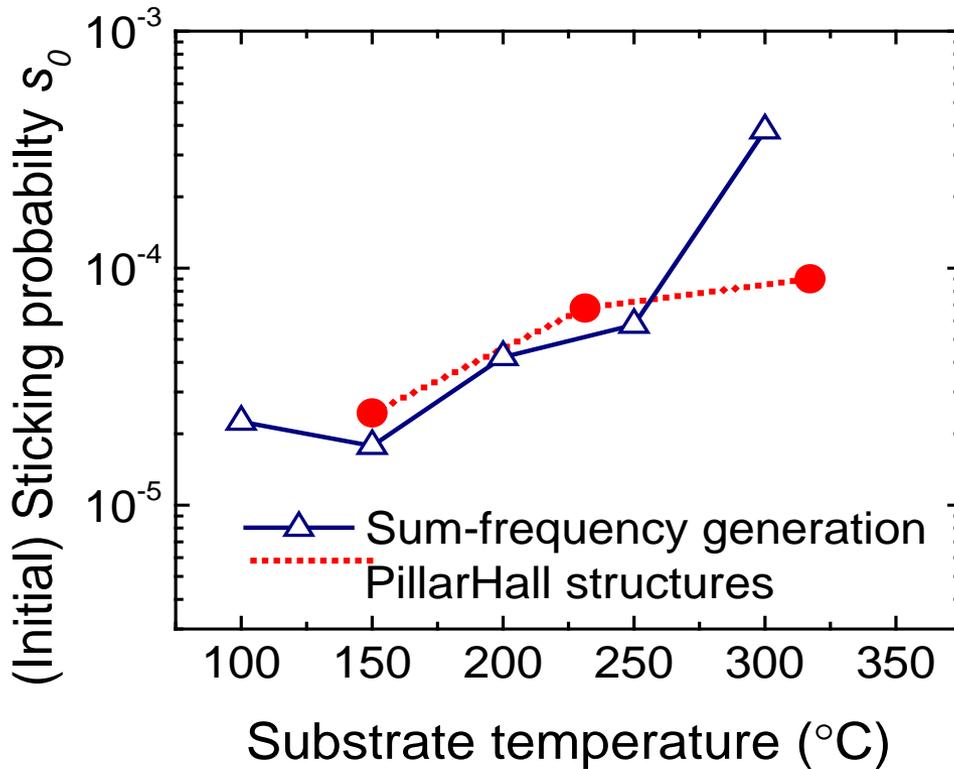
# Conformality test structures

PillarHall™ LHAR structures

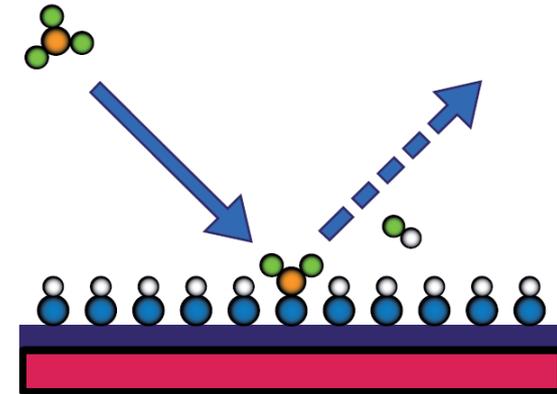


# Conformality tests – sticking probability ( $\text{Al}_2\text{O}_3$ )

Sticking probability of  $\text{H}_2\text{O}$  during  $\text{H}_2\text{O}$  step



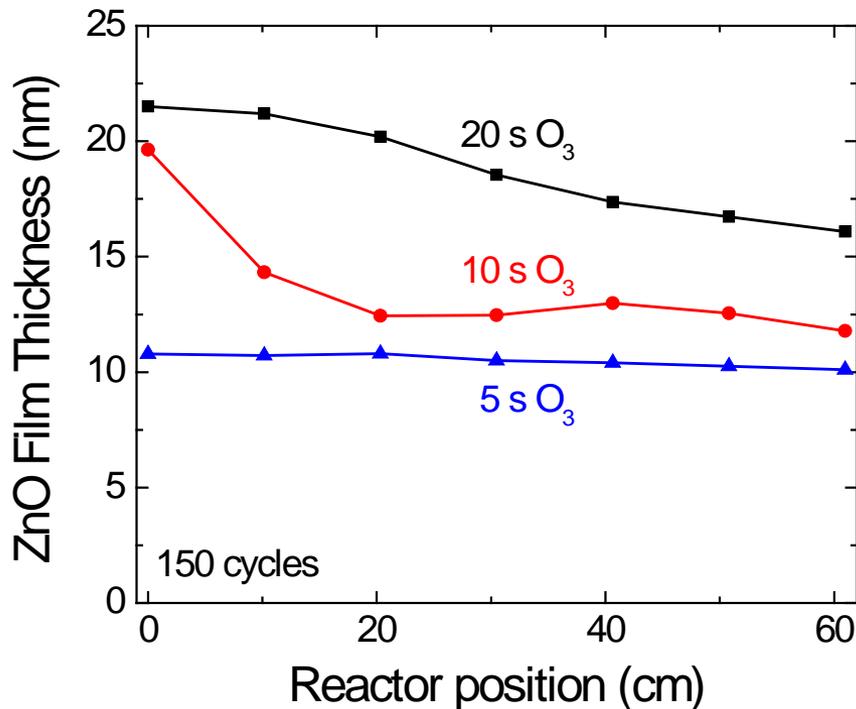
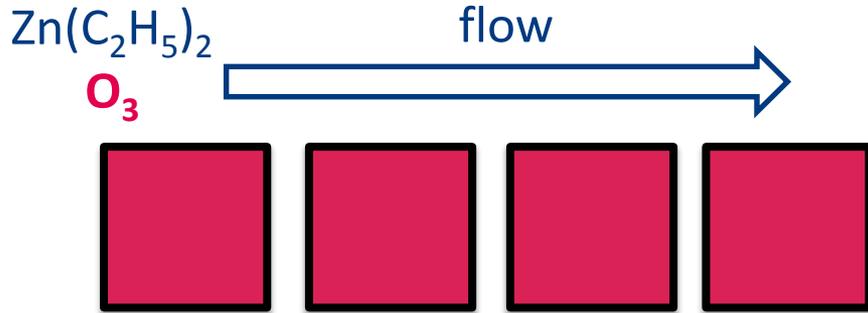
Initial sticking probability  $s_0$



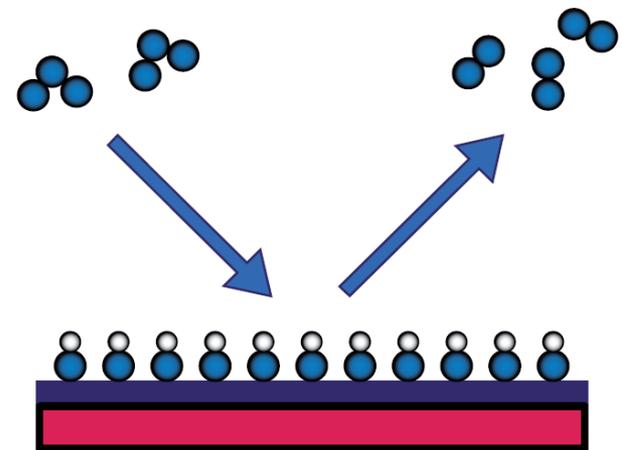
Good agreement with sum-frequency generation (SFG, see later)

Sticking probability of  $\text{H}_2\text{O} < 10^{-4} \Rightarrow \text{H}_2\text{O}$  is **not very reactive** with  $-\text{CH}_3$

# Uniformity – O<sub>3</sub> surface loss (ZnO)

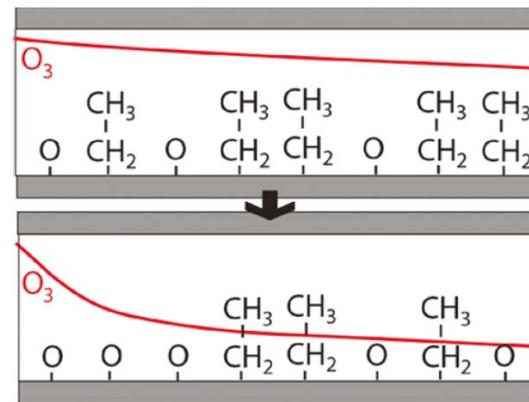
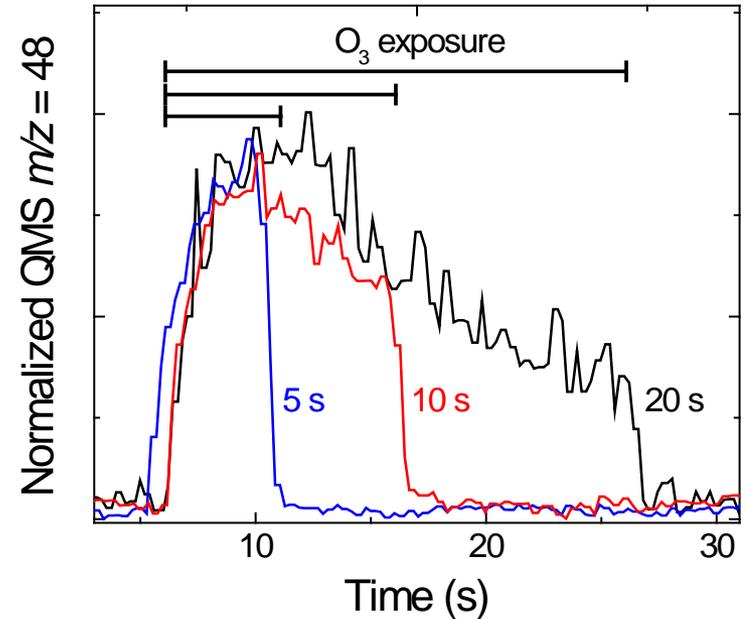
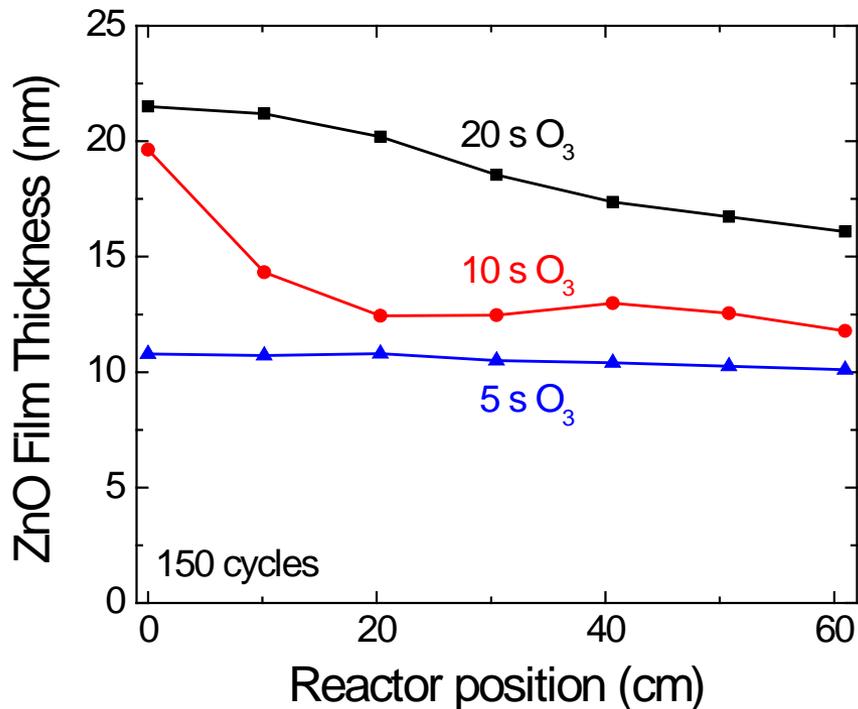
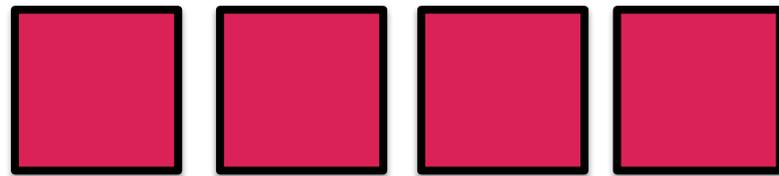


Surface loss/recombination of O<sub>3</sub>



Depends on **surface termination**

# Uniformity – O<sub>3</sub> surface loss (ZnO)



C<sub>2</sub>H<sub>5</sub>-term. surface  
Low O<sub>3</sub> loss

ZnO surface  
High O<sub>3</sub> loss

# Growth control - initial growth on foreign surfaces

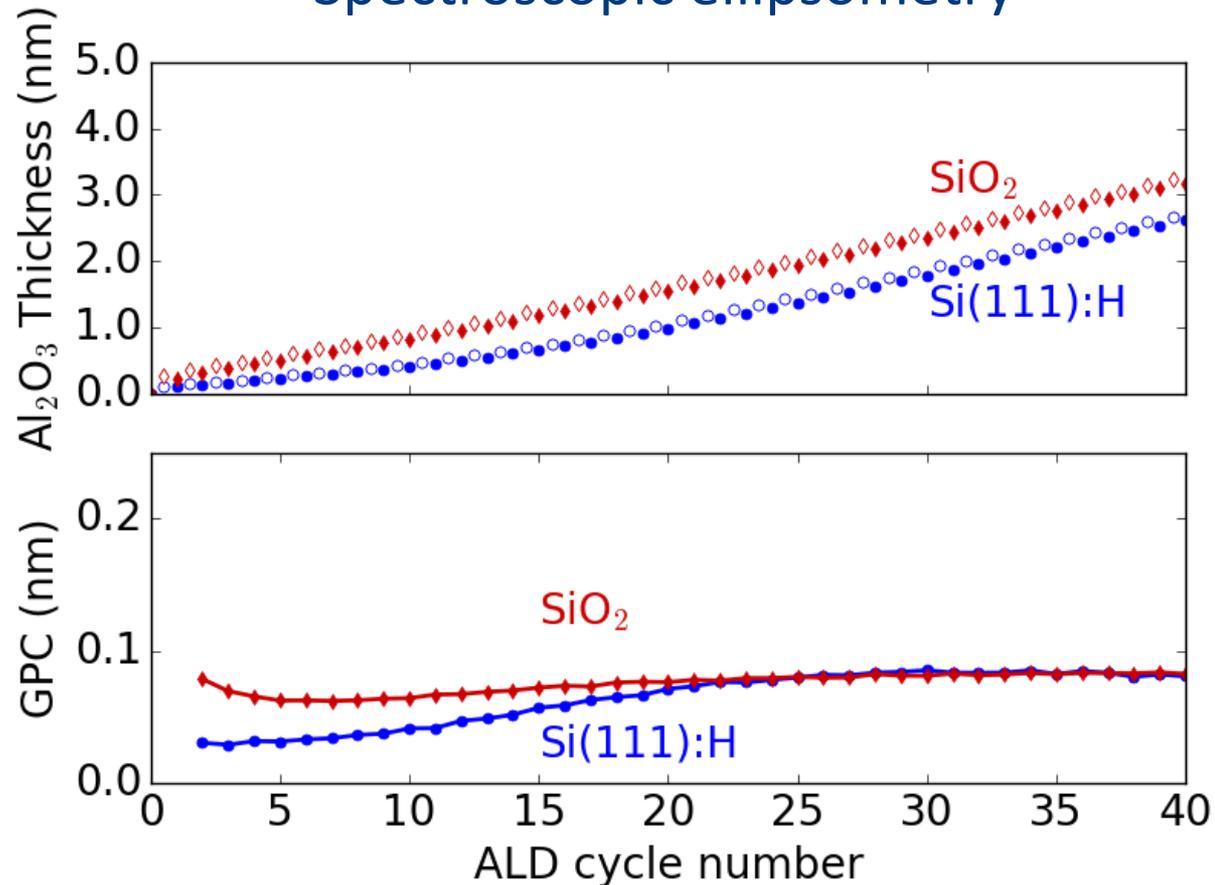
ALD  $\text{Al}_2\text{O}_3$  on  $\text{SiO}_2$  and  $\text{Si}(111):\text{H}$  surfaces

Spectroscopic ellipsometry

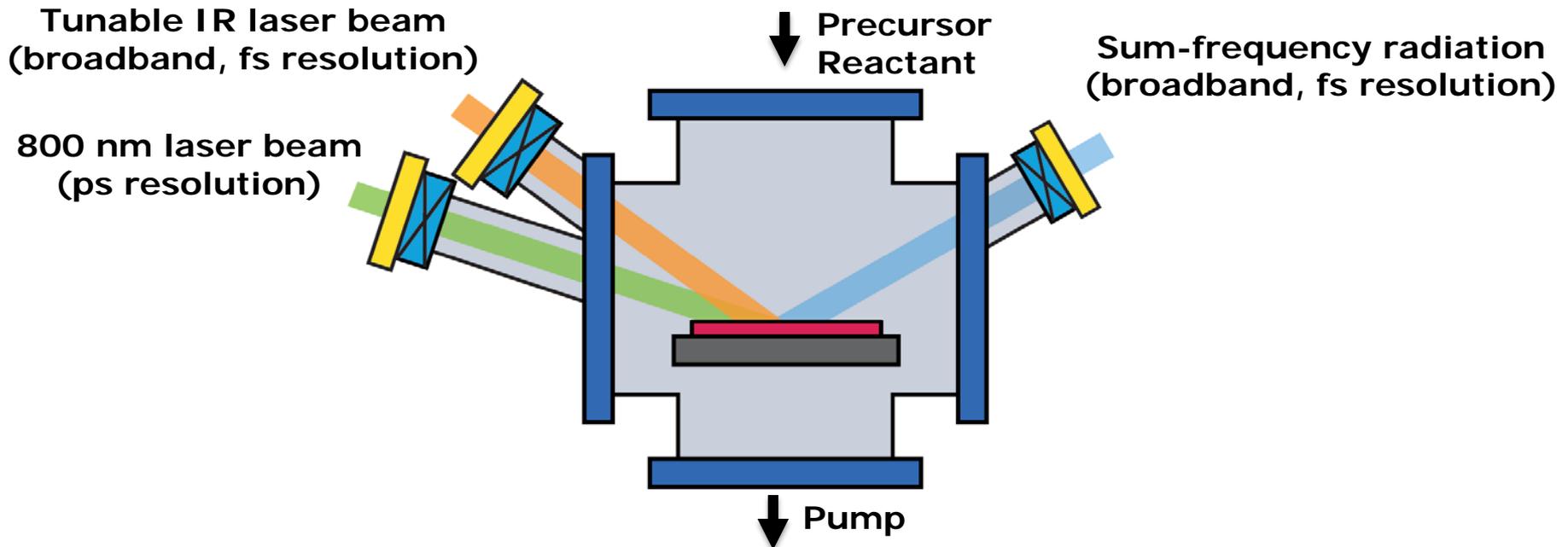
On foreign surfaces  
initially **no “ideal”**  
ALD film growth

Additional insight is  
necessary for

- Ultrathin films
- Area-selective ALD
- Etc.



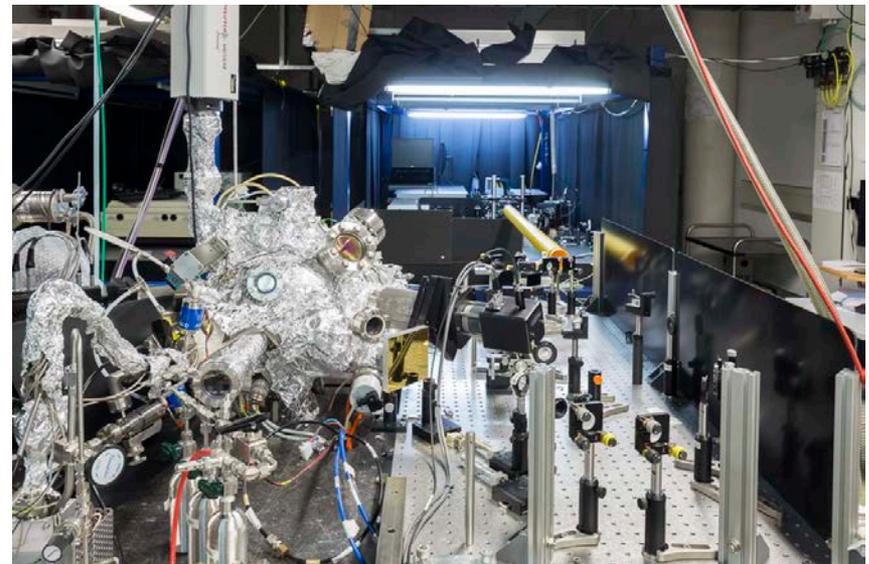
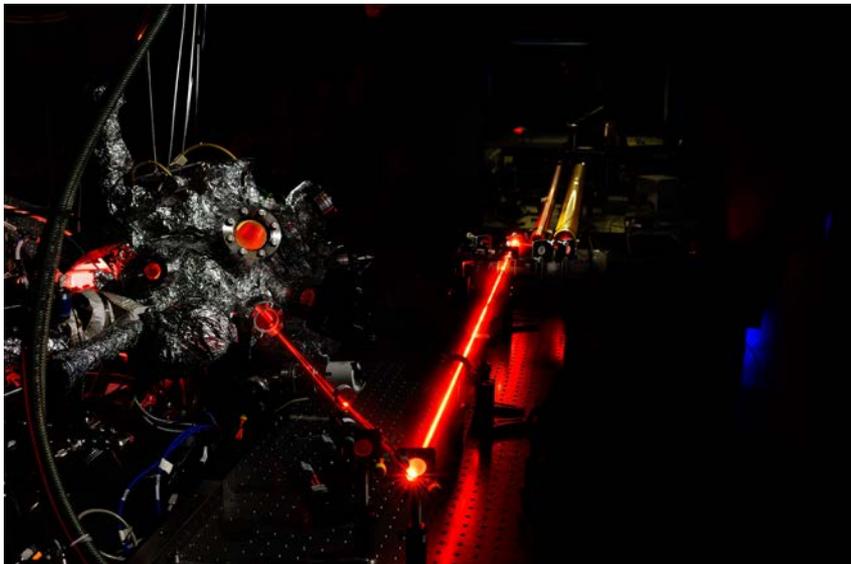
# Sum frequency generation (SFG)



## Nonlinear optical technique with 2 laser beams probing vibrational transitions

- ▲ • Highly sensitive & specific for surface groups (sub-surface species not probed)
- ▲ • Good time resolution, reaction kinetics can be followed in time
- ▲ • Can give absolute values of reaction cross-sections/sticking probabilities etc.
- ▼ • Very complex method requiring highly dedicated setup with laser-system

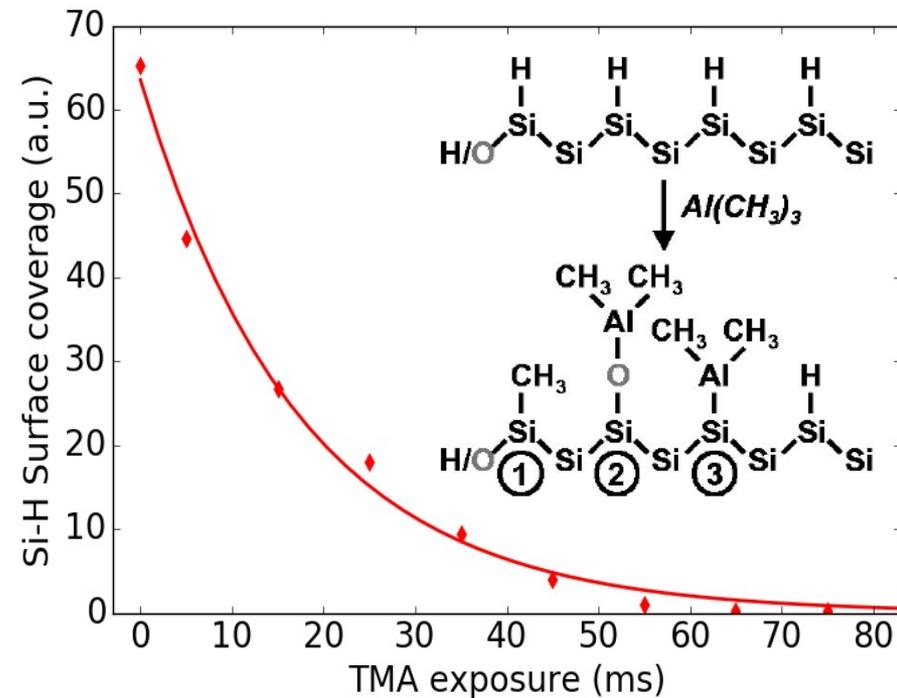
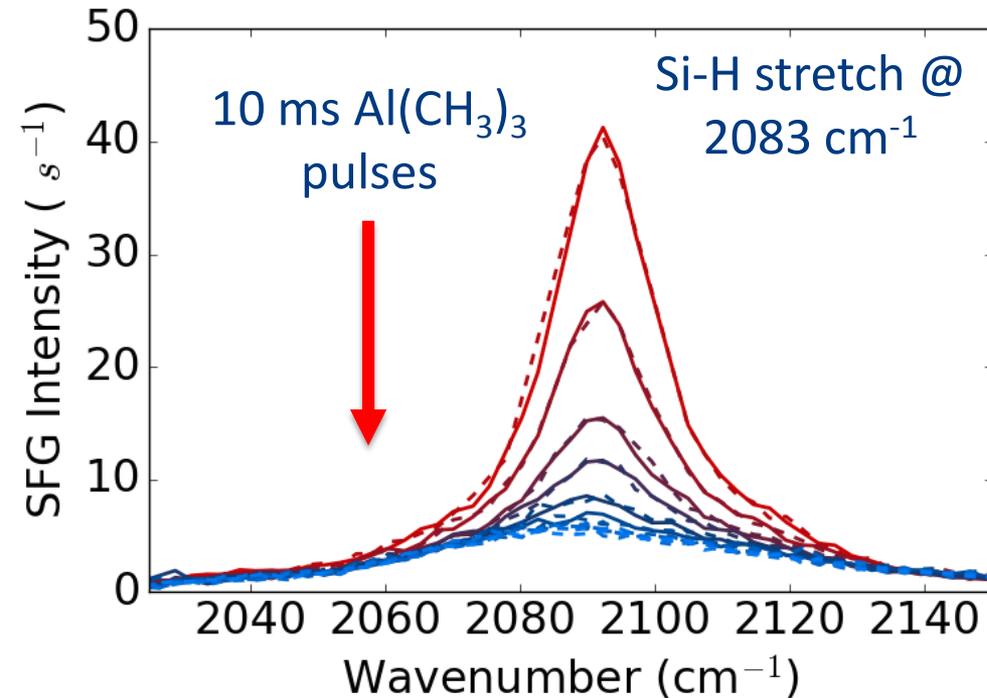
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# Sum frequency generation – Al<sub>2</sub>O<sub>3</sub> on Si(111):H



Al(CH<sub>3</sub>)<sub>3</sub> reacts with Si(111):H breaking the Si-H bonds

Reaction cross-section  $\sigma = (3.1 \pm 0.3) \times 10^{-18} \text{ cm}^2$

or translated into sticking probability  $s_0 = (1.9 \pm 0.2) \times 10^{-3}$

# Initial growth of Al<sub>2</sub>O<sub>3</sub> on SiO<sub>2</sub> and on Si(111):H

Initial growth:

**1<sup>st</sup> cycle on Si(111):H**

$$s_0 = (1.9 \pm 0.2) \times 10^{-3}$$

**1<sup>st</sup> cycle on SiO<sub>2</sub>**

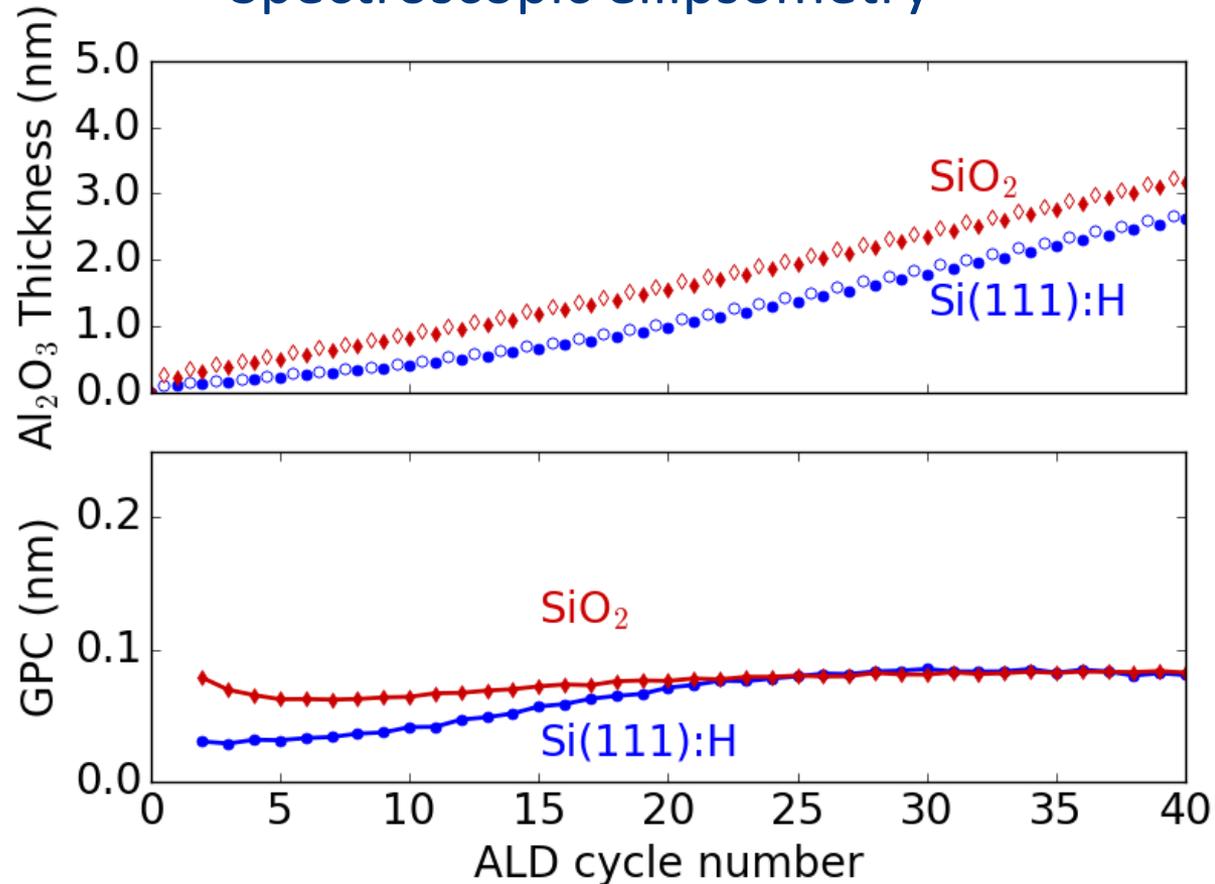
$$s_0 = (1.2 \pm 0.1) \times 10^{-3}$$

Steady-state growth:

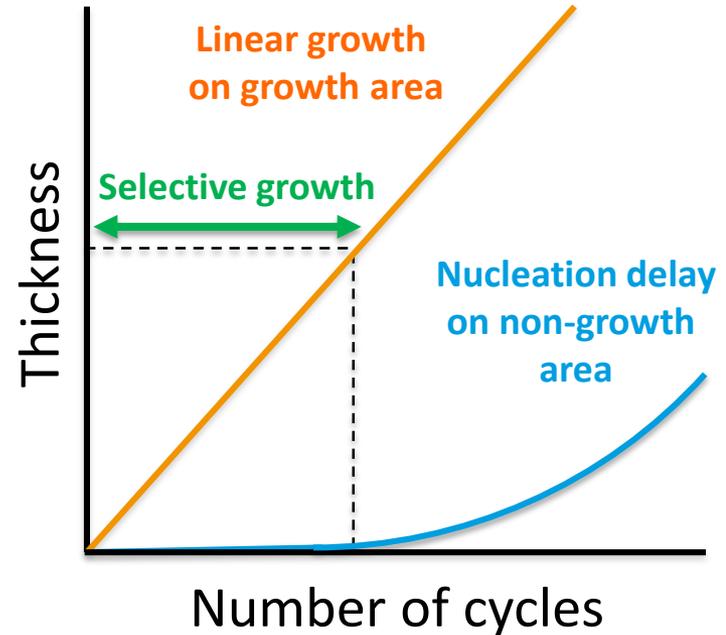
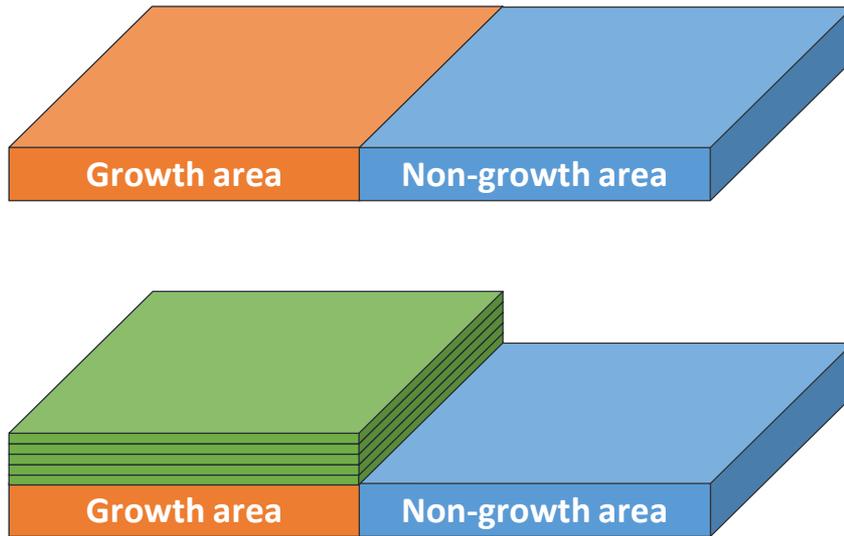
**x-th cycle (x >> 1)**

$$s_0 = (3.9 \pm 0.4) \times 10^{-3}$$

Spectroscopic ellipsometry



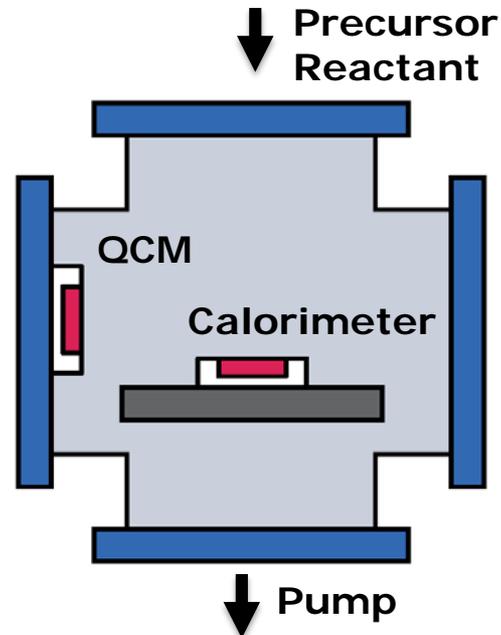
# Area-selective ALD (see tutorial Parsons)



Differences in nucleation behavior (initial growth) are often exploited to achieve area-selective ALD

**Fundamental insight (preferable with quantitative information) in initial growth is required**

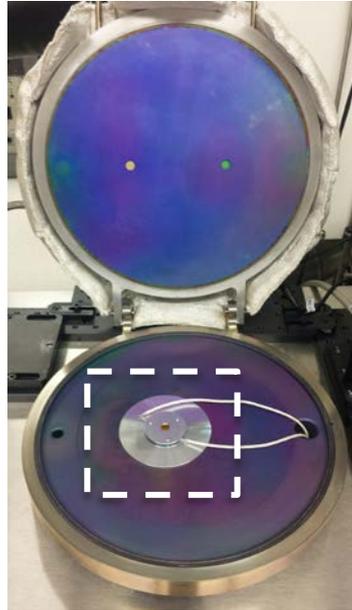
# Adsorption calorimetry



**Measures half-cycle reaction heats pyroelectrically using a  $\text{LiTaO}_3$  crystal disk**

- ▲ . Provides additional thermodynamic and mechanistic insight
- ▲ . Can be used to verify and benchmark (half-cycle) reactions – also from DFT
- ▼ . New to the field of ALD – needs follow up work
- ▼ . ....

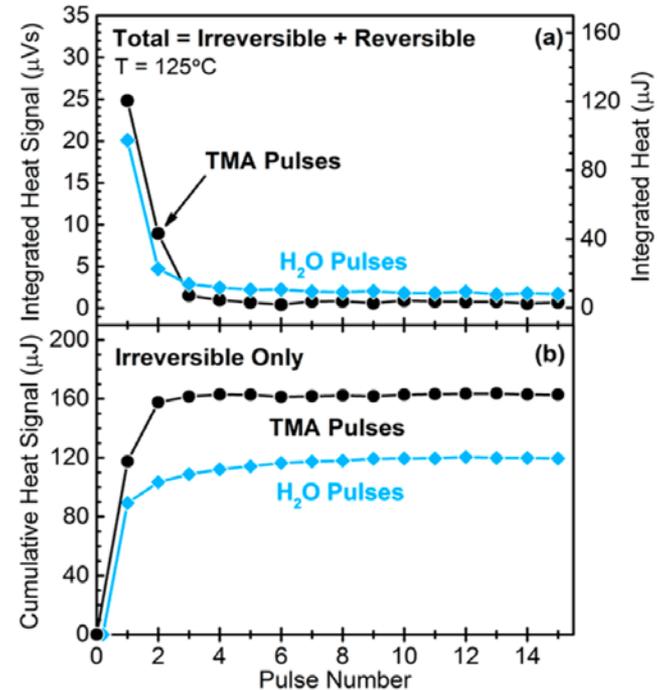
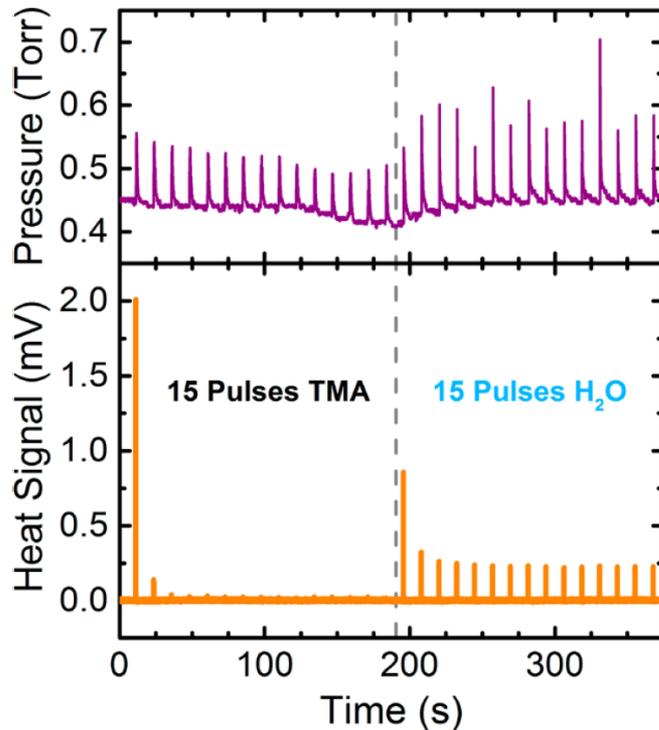
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# Adsorption calorimetry – Reaction heats ( $\text{Al}_2\text{O}_3$ )



**A - 1<sup>st</sup> Half Cycle:**

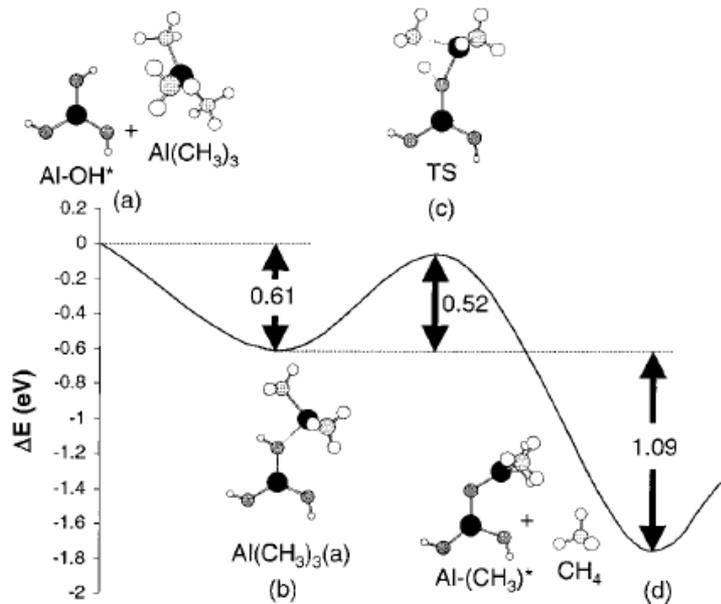


**B - 2<sup>nd</sup> Half Cycle:**

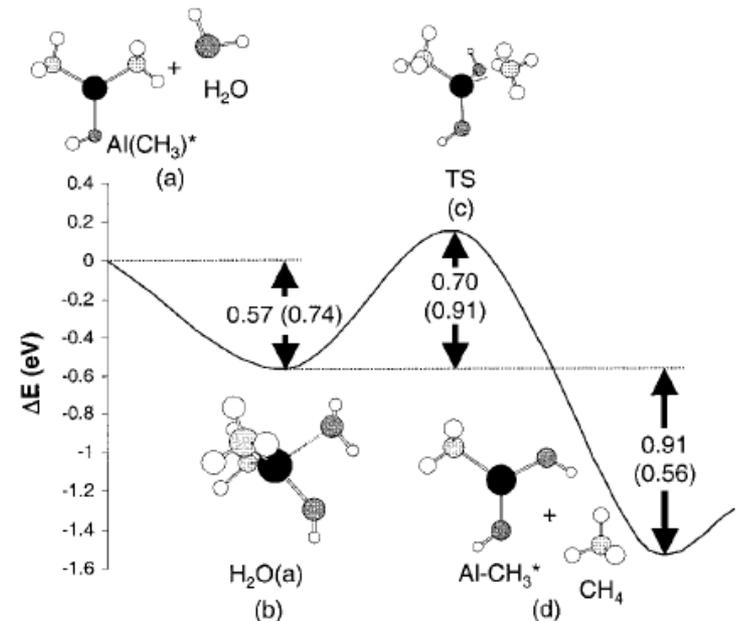


# First-principle calculations

## A - 1<sup>st</sup> Half Cycle



## B - 2<sup>nd</sup> Half Cycle

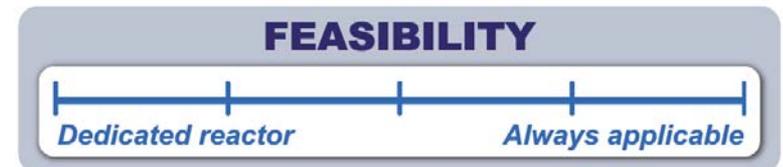
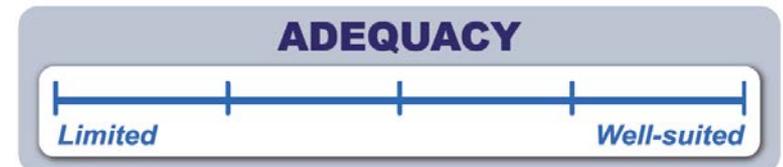


So far calculated reaction heats have remained  
untested with respect to experiment

# Concluding remarks

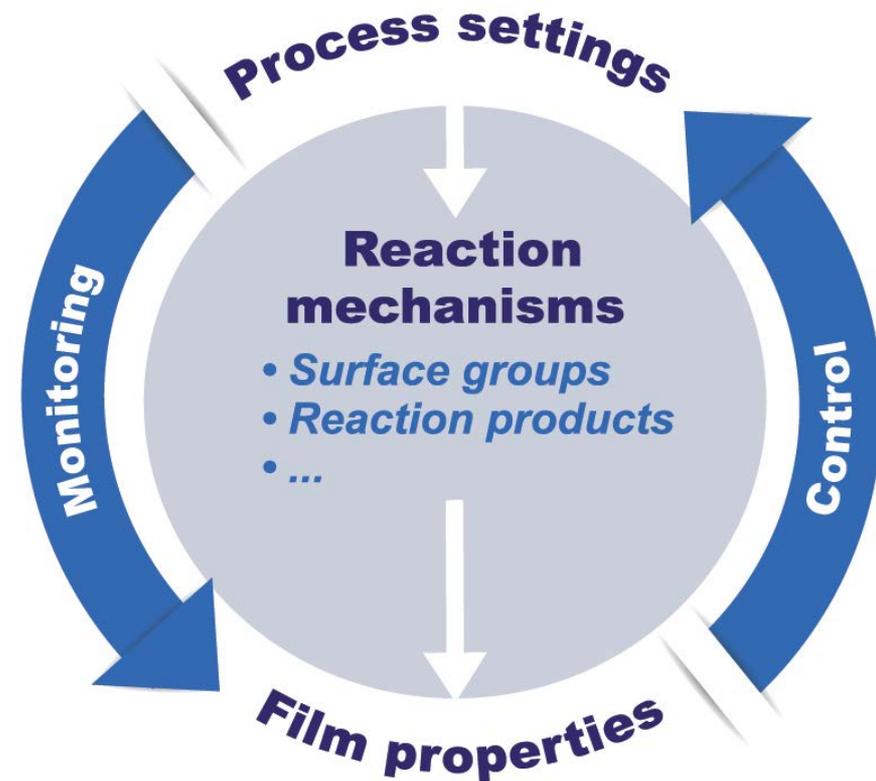
- Various analytical tools for *in situ* studies of ALD have been discussed  
QMS, gas phase FTIR, QCM, SE, surface FTIR, OES

**Many more exist. Combine tools if you can!**



# Concluding remarks

- Various analytical tools for *in situ* studies of ALD have been discussed  
QMS, gas phase FTIR, QCM, SE, surface FTIR, OES  
**Many more exist. Combine tools if you can!**
- Focus can be on
  - Film growth & properties
  - Reaction mechanisms
  - Process monitoring & control



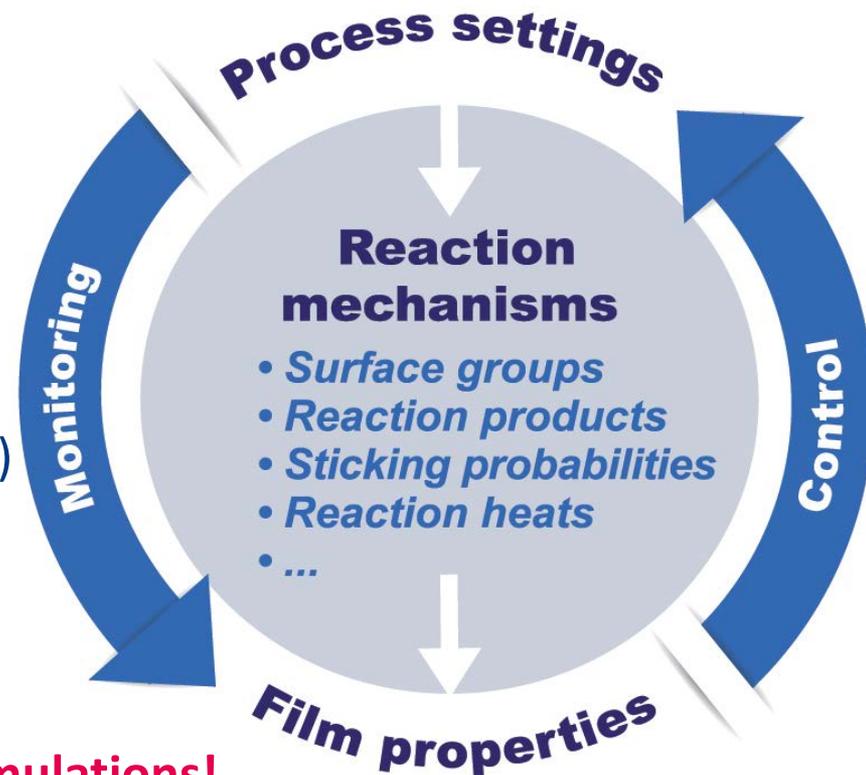
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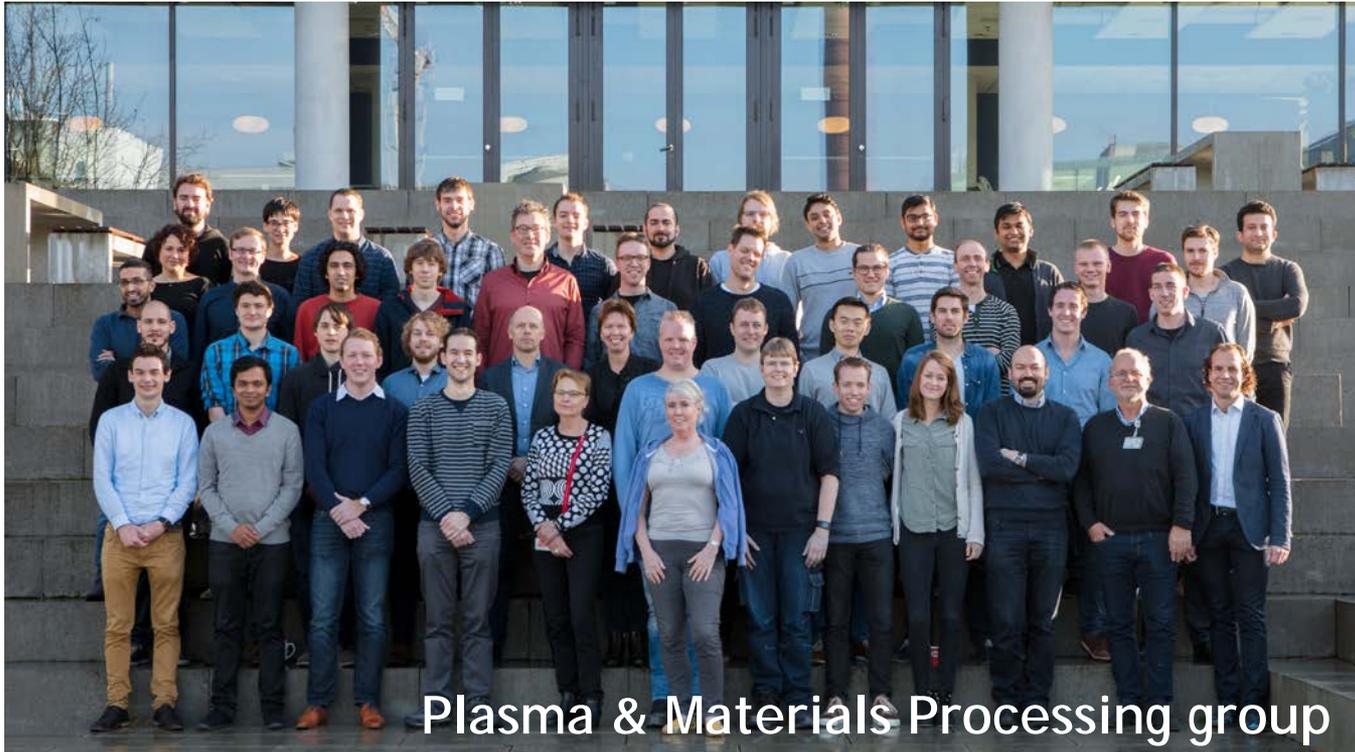
**Many more exist. Combine tools if you can!**

- Focus can be on
  - Film growth & properties
  - Reaction mechanisms
  - Process monitoring & control
- Take it to the next level (**quantitatively!**)
  - Sticking probabilities
  - Reaction heats
  - Transient states
  - ....

**Combine experiments with theory/simulations!**



# Acknowledgements



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Dr. Adrie Mackus  
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Dr. Fred Roozeboom  
Dr. Marcel Verheijen  
Dr. Ageeth Bol  
Dr. Adriana Creatore  
&  
Many PhD students  
and postdocs



For more information & feedback  
see blog:

[www.AtomicLimits.com](http://www.AtomicLimits.com)



Mission: educate students and professionals on the principles, applications and future advancements of ALD and related atomic-scale processes.



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Eindhoven University of Technology*